Using the UCD3138PSFBEVM-027

User's Guide



Literature Number: SLUUAK4 August 2013



WARNING

Always follow TI's set-up and application instructions, including use of all interface components within their recommended electrical rated voltage and power limits. Always use electrical safety precautions to help ensure your personal safety and the safety of those working around you. Contact TI's Product Information Center http://support/ti./com for further information.

Save all warnings and instructions for future reference.

Failure to follow warnings and instructions may result in personal injury, property damage, or death due to electrical shock and/or burn hazards.

The term TI HV EVM refers to an electronic device typically provided as an open framed, unenclosed printed circuit board assembly. It is intended strictly for use in development laboratory environments, solely for qualified professional users having training, expertise, and knowledge of electrical safety risks in development and application of high-voltage electrical circuits. Any other use and/or application are strictly prohibited by Texas Instruments. If you are not suitably qualified, you should immediately stop from further use of the HV EVM.

1. Work Area Safety:

- (a) Keep work area clean and orderly.
- (b) Qualified observer(s) must be present anytime circuits are energized.
- (c) Effective barriers and signage must be present in the area where the TI HV EVM and its interface electronics are energized, indicating operation of accessible high voltages may be present, for the purpose of protecting inadvertent access.
- (d) All interface circuits, power supplies, evaluation modules, instruments, meters, scopes and other related apparatus used in a development environment exceeding 50 V_{RMS}/75 VDC must be electrically located within a protected Emergency Power Off (EPO) protected power strip.
- (e) Use a stable and non-conductive work surface.
- (f) Use adequately insulated clamps and wires to attach measurement probes and instruments. No freehand testing whenever possible.

2. Electrical Safety:

- (a) De-energize the TI HV EVM and all its inputs, outputs, and electrical loads before performing any electrical or other diagnostic measurements. Revalidate that TI HV EVM power has been safely deenergized.
- (b) With the EVM confirmed de-energized, proceed with required electrical circuit configurations, wiring, measurement equipment hook-ups and other application needs, while still assuming the EVM circuit and measuring instruments are electrically live.
- (c) Once EVM readiness is complete, energize the EVM as intended.

WARNING: while the EVM is energized, never touch the EVM or its electrical circuits as they could be at high voltages capable of causing electrical shock hazard.

3. Personal Safety:

(a) Wear personal protective equipment e.g. latex gloves and/or safety glasses with side shields or protect EVM in an adequate lucent plastic box with interlocks from accidental touch.

4. Limitation for Safe Use:

(a) EVMs are not to be used as all or part of a production unit.

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Using the UCD3138PSFBEVM-027

1 Introduction

This evaluation model (EVM), the UCD3138PSFBEVM-027, is used to evaluate the UCD3138 64-pin digital control IC in an off-line power-converter application and then to aid in its design. The EVM is a standalone phase-shifted full-bridge DC-DC power converter. The EVM is used together with a control card, the UCD3138CC64EVM-030, which is an EVM placed on the UCD3138RGC.

The UCD3138PSFBEVM-027, together with the UCD3138CC64EVM-030, evaluates a phase-shifted fullbridge DC-DC converter. Each EVM is delivered without requiring additional work, from either hardware or firmware. This EVM combination allows for some of the design parameters to be retuned using Texas Instruments' graphical user interface (GUI) based tool, Fusion Digital Power[™] Designer. Loading custom firmware with user-designed definition and development is also possible.

Three EVMs are included in the kit: the UCD3138PSFBEVM-027, UCD3138CC64EVM-030, and USB-TO-GPIO.

This user's guide provides basic evaluation instruction with a focus on system operation in a standalone phase-shifted full-bridge DC-DC power converter.

WARNING
High voltages are present on this evaluation module during operation and for a a time period after power off. This module should only be tested by skilled personnel in a controlled laboratory environment.
An isolated DC voltage source meeting IEC61010 reinforced insulation standards is recommended for evaluating this EVM.
High temperature exceeding 60°C may be found during EVM operation and for a time period after power off.
The purpose of this EVM is to facilitate the evaluation of digital control in a phase-shifted full-bridge DC-DC converter using the UCD3138, and cannot be tested and treated as a final product.
Extreme caution should be taken to eliminate the possibility of electric shock and heat burn. Please refer to the page <i>Evaluation</i> Module Electrical Safety Guideline after the cover page for your safety concerns and precautions.
Read and understand this user's guide thoroughly before starting any physical evaluation.

3



Description

2 Description

The UCD3138PSFBEVM-027, along with the UCD3138CC64EVM-030, demonstrates a phase-shifted fullbridge DC-DC power converter with digital control using the UCD3138 device. The UCD3138 device is located on the UCD3138CC64EVM-030 board. The UCD3138CC64EVM-030 is a daughter-card with preloaded firmware providing the required control functions for an phase-shifted full-bridge converter. Please contact TI for details on the firmware. The UCD3138PSFBEVM-027 accepts a DC input from 370 to 400 VDC, and outputs a typical 12 VDC with full-load output power at 360 W, or full output current of 30 A.

NOTE: This EVM does not have an input fuse. It relies on the input current limit from the input voltage source that is used.

2.1 Typical Applications

- Offline DC-DC power conversions
- Servers
- Telecommunication systems

2.2 Features

- Digitally-controlled phase-shifted full-bridge DC-DC power conversion
- DC input from 370 to 400 VDC
- 12-VDC regulated output from no load to full load
- Full-load power at 360 W, or full-load current at 30 A
- High efficiency
- Constant soft-start time
- Overvoltage, overcurrent, and brownout protection
- Test points to facilitate device and topology evaluation

4



3 Performance Specifications

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Input Characteristics				I	
Voltage operation range		370		400	VDC
Input UVLO On			350		VDC
Input UVLO Off			330		VDC
	Input = 370 VDC, full load = 30 A			1.2	
Input current	Input = 385 VDC, full load = 30 A			1.1	А
	Input = 400 VDC, full load = 30 A			1	
Output Characteristic	S			L. L	
Output voltage, VOUT	No load to full load		12		VDC
Output over voltage			13.5		VDC
Output load current, IOUT ⁽¹⁾	370 to 400 VDC			30	А
Output voltage ripple	385 VDC and full load = 30 A		90		mVpp
Output over current		30			А
Systems Characterist	ics			· · ·	
Switching frequency			140		kHz
Peak efficiency	385 VDC, full load = 30 A		93.5		%
Full-load efficiency	385 VDC, load = 30 A		93.5		%
Operating temperature 400-LFM forced air flow cooling			25		°C
Firmware	•				
Device ID (Version)	UCD3100ISO1 0.0.01.0001 130315			1	
Filename	UCD3138PSFBPWR027_03152013.x0				

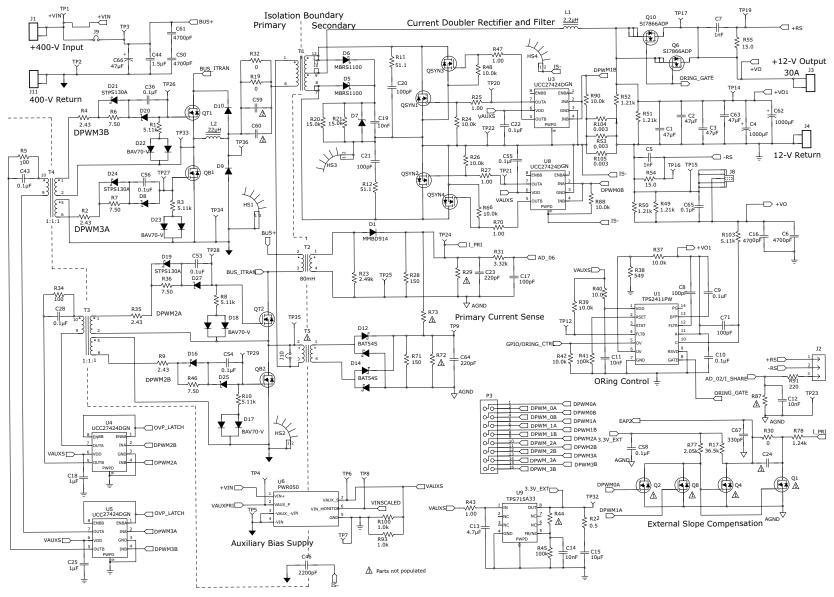
Table 1. UCD3138PSFBEVM-027 Performance Specifications⁽¹⁾

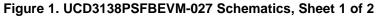
⁽¹⁾ The load current and load power are commanded using the designer GUI. See Section 12 for more information on CPCC operation. See Section 13 for more information on GUI application.

5

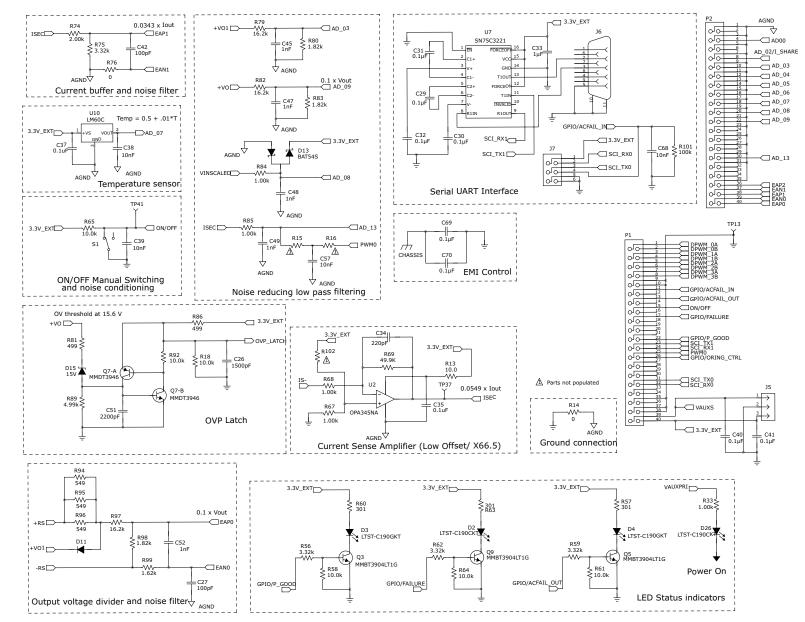


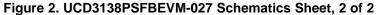
4 Schematics











Schematics

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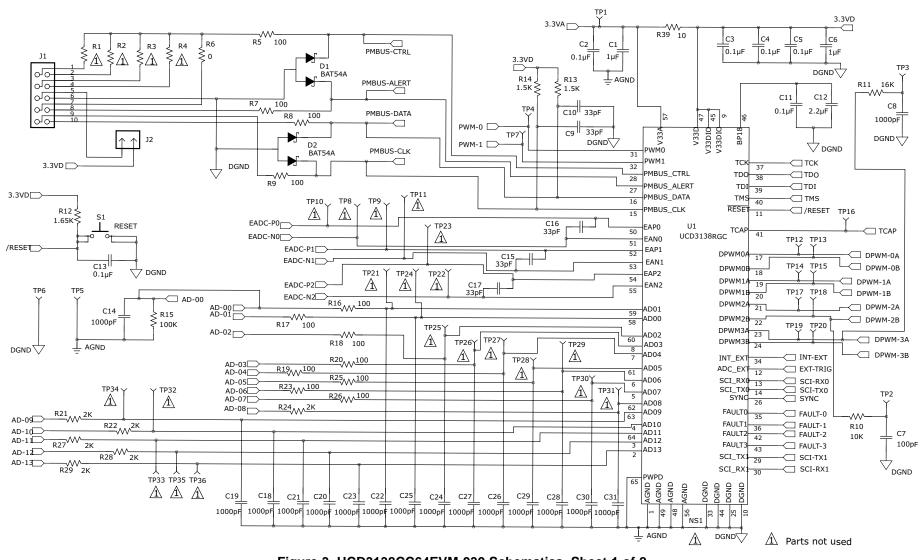
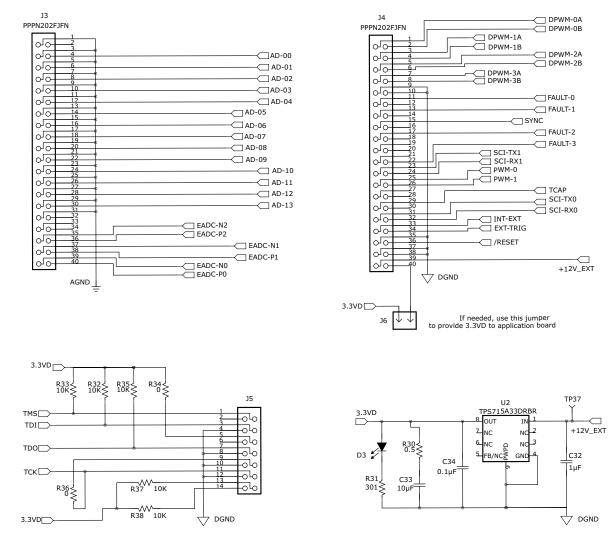


Figure 3. UCD3138CC64EVM-030 Schematics, Sheet 1 of 2







5 Test Setup

5.1 Test Equipment

DC voltage source: This source is capable of 350 to 400 VDC. The source is adjustable, with a minimum power rating of 400 W, or current rating no less than 1.5 A, and has a current limit function. The DC voltage source used should meet IEC61010 safety requirements.

DC multi-meter: The multi-meter has two units, one is capable of a 0 to 400 VDC input range and preferred four-digit display. The other unit is capable of a 0 to 15 VDC input range and a preferred four-digit display.

Output load: This DC load is capable of receiving 0 to 15 VDC, 0 to 30 A, and 0 to 360-W or greater, with display such as load current and load power.

Current meter: If the load does not have a display, this DC current-meter is optional. This unit is capable of 0 to 30 A. A low-ohmic shunt and DMM are recommended.

Oscilloscope: The oscilloscope is capable of 500-MHz full bandwidth, digital or analog. If choosing a digital oscilloscope, TI recommends 5 Gs/s or better.

Fan: A fan with 400-LFM forced-air cooling is required.

Recommended wire gauge: The recommended gauge must be capable of 30 A, or better than No. 14 AWG, with the total wire length less than 8 ft (4-ft input and 4-ft return).

5.2 Recommended Test Setup

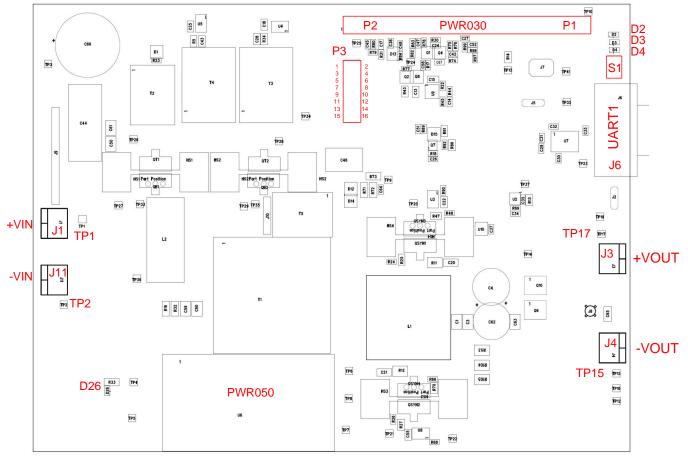


Figure 5. UCD3138PSFBEVM-027 Recommended Test Setup





Figure 6. Orientation of the UCD3138CC64EVM-030 Board on the UCD3138PSFBEVM-027 Board

6 Test Points

Test Points	Name	Description
TP1	+VIN	Positive input voltage
TP2	–VIN	Input voltage return
TP3	BUS+	Primary high-side current-sense input
TP4	VAUXPRI	Primary 12-V bias
TP5	PWRGND	Primary 12-V bias return
TP6	VAUX_S	Secondary 12-V bias
TP7	PGND	Secondary 12-V bias return
TP8	VINSCALED	VIN sense on the secondary side
TP9	Ipri	Primary current sense
TP10		Control-card mechanical-guide pin
TP11	Not used	
TP12	FLTB	Oring control
TP13	PGND	Secondary 12-V bias return
TP14	+VO1	Output before oring FETs
TP15	PGND	Secondary 12-V bias return
TP16	–RS	Remote sense of the output voltage
TP17	VO	Output voltage positive terminal
TP18	Not used	
TP19	+RS	Remote sense of the output voltage
TP20	SR1-3	QSYN 1 and 3 drive
TP21	SR2-4	QSYN 2 and 4 drive
TP22	IS-	Load current sense
TP23	AGND	Analog ground
TP24	Ipri	Primary current sense (AD_06)

Table 2. UCD3138PSFBEVM-027 List of Test Points

Test Points	Name	Description
TP25	AGND	Analog ground
TP26	QT1_Gate	QT1 gate
TP27	QB1_Gate	QB1 gate
TP28	QT2_Gate	QT2 gate
TP29	QB2_Gate	QB2 gate
TP30	Not used	
TP31	Not used	
TP32	3.3V	3.3 V
TP33	SW1	Switch node
TP34	PWRGND	Primary 12-V bias return
TP35	SW2	Switch Node
TP36	CASS	Primary commutation-assist junction
TP37	ISEC	IOUT sensing output (EADC1 Input)
TP38	Not used	
TP39	Not used	
TP40	Not used	
TP41	S1	S1 status

Table 2. UCD3138PSFBEVM-027 List of Test Points (continued)

7 Terminals

Table 3. List of Terminals

Terminal	Name	Description
J1 Input_P		Input voltage positive terminal
J2	Remote Sense	Remote sense and I_SHARE
J3	12VO	+12-V output
J4	-12VO	12-V output return
J5	Bias	VAUX_S and 3.3V_EXT
J6	UART1	Standard UART connection, RS232, 9-pin
J7	UART0	UART0 and ACFAIL_IN (communication with PFC)
J8	VO_RIPPLE	BNC VO_Ripple
J9	Jumper	Jumper (reserved to an input-fuse substitution)
J10	Jumper	Used when T5 not populated
J11	Input_N	Input voltage return terminal



8 Test Procedure

8.1 Efficiency Measurement Procedure

WARNING

Danger of electrical shock! High voltage present during measurement!

CAUTION

Do not leave the EVM powered when unattended.

CAUTION

Danger of heat burn from high temperature.

- 1. See Figure 4 for basic setup to measure power-conversion efficiency. The required equipment for this measurement is listed in Figure 5.
- 2. Check the boards visually before making electrical connections to ensure that no shipping damage occurred.
- 3. Use the UCD3138PSFBEVM-027 and UCD3138CC64EVM-030 for this measurement which are included this EVM package along with the USB-TO-GPIO.
- 4. Install the UCD3138CC64EVM-030 board onto the UCD3138PSFBEVM-027 first. Take care with the alignment and orientation of the two boards to avoid damage.
 - See Figure 6 for the UCD3138PFCEVM-030 board orientation.
- 5. Connect the DC-voltage source to J1 (+) and J11 (–). The DC-voltage source should be isolated and meet IEC61010 requirements.
 - Set up the DC-output voltage in the range specified in Table 1, between 370 VDC and 400V DC; set the DC-source current limit at 1.2 A.
 - **NOTE:** A fuse is not installed on the board and, therefore, the board relies on the current limit of the external voltage source for circuit protection.
- 6. Connect an electronic load with either a constant-current mode or constant-resistance mode. The load range is from 0 to 30 A.
- 7. Ensure a jumper is installed on J6 of the UCD3138CC64EVM-030
- 8. Use the switch S1 to turn on the board output after the input voltage is applied to the board. Before applying input voltage, ensure that the switch, S1, is in the *OFF* position.
- 9. Use a current meter or low-ohmic shunt and DMM between the load and the board for current measurements if the load does not have a current or a power display.
- 10. Connect a volt-meter across the output connector and set the volt-meter scale at 0 to 15 V (DC).
- 11. Turn on the DC-voltage source output. Flip S1 to ON and vary the load.
- 12. Record output voltage and current measurements.

8.2 Equipment Shutdown Procedure

- 1. Shut down the DC-voltage source
- 2. Shut down the electronic load.

Test Procedure



9 **Performance Data and Typical Characteristics Curves**

Figure 7, Figure 8, Figure 9, Figure 10, Figure 11, Figure 9, Figure 10, Figure 12, Figure 13, Figure 14, and Figure 15 present typical performance curves for the UCD3138PSFBEVM-027.

9.1 Efficiency

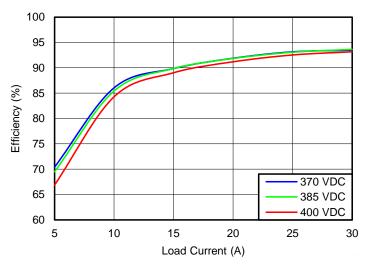


Figure 7. UCD3138PSFBEVM-027 Efficiency

9.2 Load Regulation

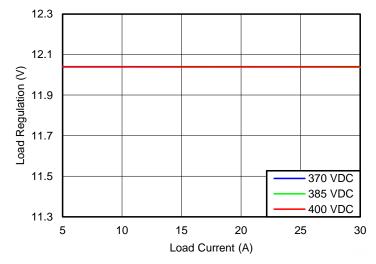
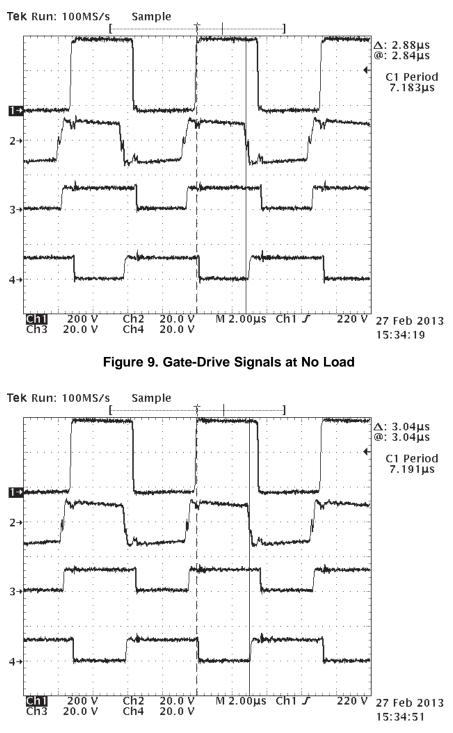
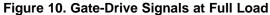


Figure 8. UCD3138PSFBEVM-027 Load Regulation



9.3 Switching Waveforms





Ch1 = QT1 gate to GND (TP26) Ch3 = QSYN1 Vgs (TP20) Ch2 = QB2 Vgs (TP29) Ch4 = QSYN2 Vgs (TP21)



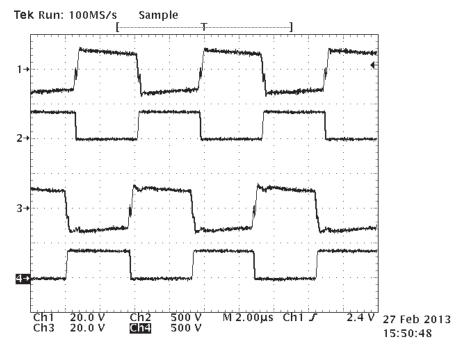


Figure 11. Primary-Side Switching

Ch1 = QB1 Vgs	Ch2 = QB1 Vds
Ch3 = QB2 Vgs	Ch4 = QB2 Vds

9.4 Output Voltage Ripple

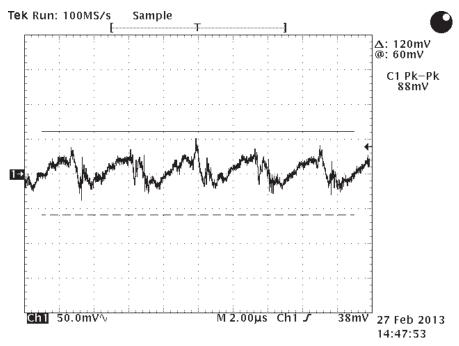


Figure 12. Output Voltage Ripple, 385 VDC and Full Load

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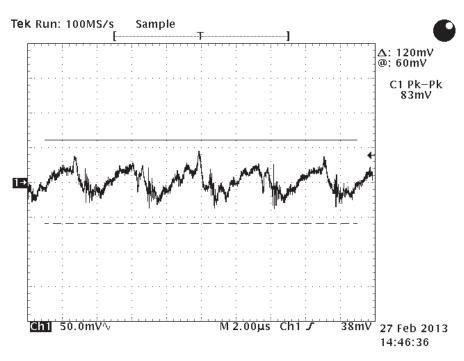


Figure 13. Output Voltage Ripple, 385 VDC and Half Load

9.5 Output Turnon

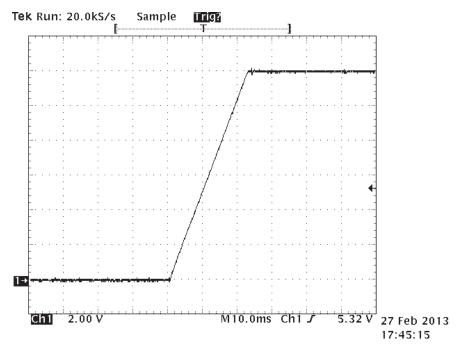


Figure 14. Output Turnon, 385 VDC With Load Range



9.6 Bode Plots

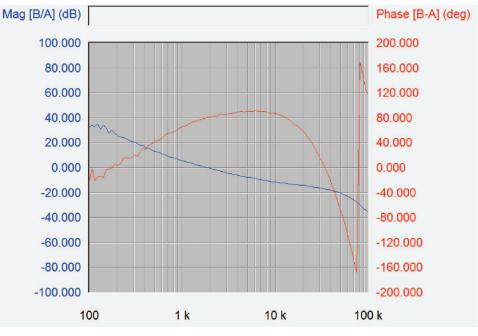


Figure 15. Control-Loop Bode Plots at 385 VDC Across Load Range

10 EVM Assembly Drawing and PCB layout

Figure 16, Figure 17, Figure 18, Figure 19, Figure 20 and Figure 21 show the design of the UCD3138PSFBEVM-027 printed circuit board (PCB). The PCB dimensions are $L \times W = 8 \times 6$ in, the PCB material is FR4, or compatible, four layers with 2-oz copper on each layer.

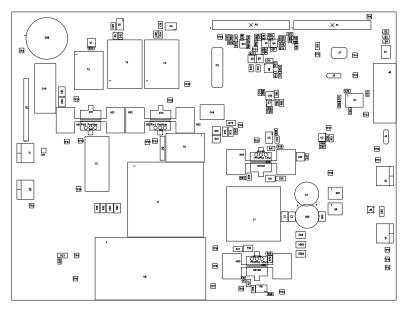


Figure 16. UCD3138PSFBEVM-027 Top-Layer Assembly Drawing (Top view)

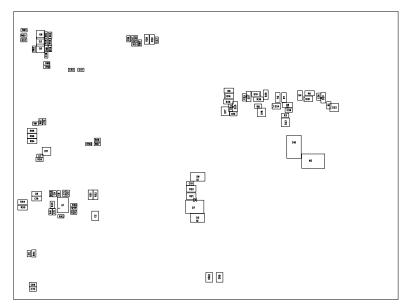


Figure 17. UCD3138PSFBEVM-027 Bottom-Layer Assembly Drawing (Bottom view)

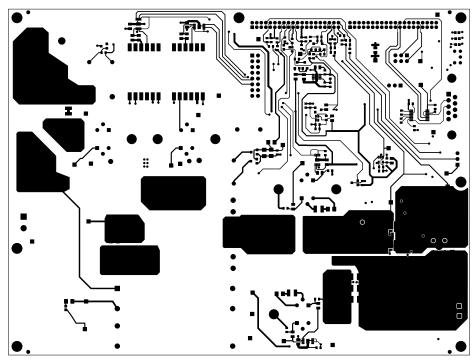


Figure 18. UCD3138PSFBEVM-027 Top Copper (Top View)



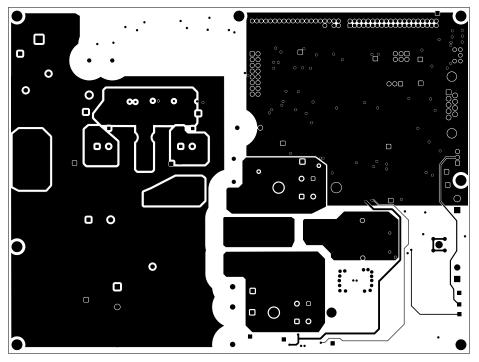


Figure 19. UCD3138PSFBEVM-027 Internal Layer, One (Top View)

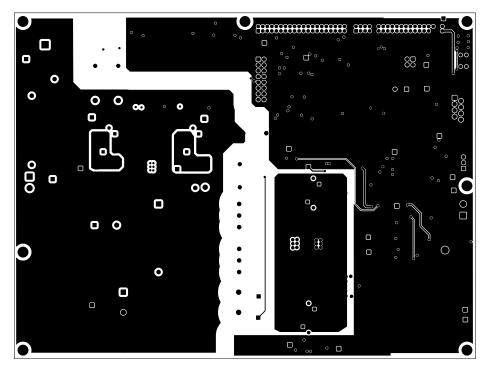


Figure 20. UCD3138PSFBEVM-027 Internal Layer, Two (Top View)



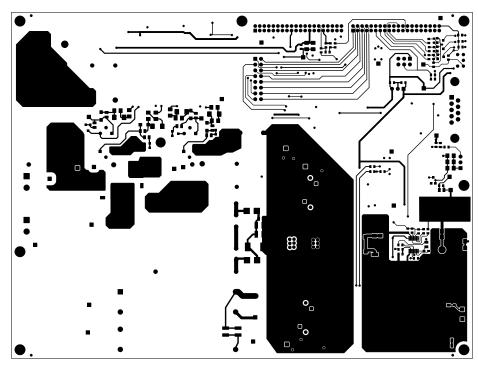


Figure 21. UCD3138PSFBCEVM-027 Bottom Copper (Top View)

11 Bill of Materials

QTY	RefDes	Value	Description	Size	Part Number	MFR
4	C1, C2, C3, C63	47 µF	Capacitor, Ceramic, 16 V, X5R, 20%	1210	STD	STD
7	C11, C12, C14, C38, C39, C57, C68	10 nF	Capacitor, Ceramic, 25 V, X7R, 10%	0603	STD	STD
1	C13	4.7 μF	Capacitor, Ceramic, 16 V, X7R, 10%	0805	STD	STD
1	C15	10 µF	Capacitor, Ceramic, 6.3 V, X7R, 10%	0805	STD	STD
3	C17, C27, C42	100 pF	Capacitor, Ceramic, 16 V, X7R, 10%	0603	STD	STD
2	C18, C25	1 µF	Capacitor, Ceramic, 25 V, X7R, 10%	0805	STD	STD
1	C19	10 nF	Capacitor, Ceramic, 100 V, X7R, 10%	0805	STD	STD
2	C20, C21	100 pF	Capacitor, Ceramic, 100 V, NP0, 10%	1206	STD	STD
10	C22, C28, C36, C43, C53, C54, C55, C56, C69, C70	0.1 µF	Capacitor, Ceramic, 25 V, X7R, 10%	0805	STD	STD
3	C23, C34, C64	220 pF	Capacitor, Ceramic, 50 V, X7R, 10%	0603	STD	STD
0	C24	Open	Capacitor, Ceramic, 16 V, X7R, 10%	0603	STD	STD
1	C26	1500 pF	Capacitor, Ceramic, 50 V, X7R, 10%	0603	STD	STD
1	C33	1 µF	Capacitor, Ceramic, 16 V, X7R, 10%	0603	STD	STD
2	C4, C62	1000 µF	Capacitor, Aluminum, SM, 25 V,	12,5 × 20 mm	EEUFM1E102	Panasonic
1	C44	1.5 µF	Capacitor, Polyester, 450 V, ±10%	1.012 × 0.322 in	ECQ-E2W155KH	Panasonic
1	C46	2200 pF	Capacitor, Ceramic Disc, Y1, 250 V, Y5U ±20%	.5 × .31 in	CD12-E2GA222MYGS	TDK
7	C5, C7, C45, C47, C48, C49, C52	1 nF	Capacitor, Ceramic, 50 V, X7R, 10%	0603	STD	STD
2	C50, C61	4700 pF	Capacitor, Ceramic, 500 V, X7R, 10%	1210	STD	STD
1	C51	2200 pF	Capacitor, Ceramic, 50 V, X7R, 10%	0603	STD	STD
0	C59, C60	Open	Capacitor	1210	STD	STD
2	C6, C16	4700 pF	Capacitor, Ceramic, 50 V, X7R, 10%	1206	STD	STD
1	C65	0.1 µF	Capacitor, Ceramic, 50 V, X7R, 10%	1206	STD	STD
1	C66	47 µF	Capacitor, Alum Electrolytic, 450 V, ±20%	10 × 20 mm	LGU2W470MELY	NichiCon

Table 4. Component List Based on the Schematics of Figure 1 and Figure 2⁽¹⁾

(1) STD = standard

TEXAS INSTRUMENTS

QTY	RefDes	Value	Description	Size	Part Number	MFR
1	C67	330 pF	Capacitor, Ceramic, 50 V, X7R, 10%	0603	STD	STD
2	C8, C71	100 pF	Capacitor, Ceramic, 50 V, X7R, 10%	0603	STD	STD
11	C9, C10, C29, C30, C31, C32, C35, C37, C40, C41, C58	0.1 µF	Capacitor, Ceramic, 25 V, X7R, 10%	0603	STD	STD
2	D1, D11	MMBD914	Diode, Switching, 100 V, 200 mA	SOT23	MMBD914	Fairchild
3	D12, D13, D14	BAT54S	Diode, Dual Schottky, 30 V, 200 mA	SOT23	BAT54S	Vishay
1	D15	15 V	Diode, Zener, 15 V, 8. 5mA	SOT23	MMBZ5245BLT1G	Diodes
4	D16, D19, D21, D24	STPS130A	Diode, Power Schottky, 30 V, 1 A	SMA	STPS130A	ST
4	D17, D18, D22, D23	BAV70-V	Diode, Switching, Dual, 70 V, 250 mA	SOT23	BAV70-V-GS08	Zetex
2	D2, D26	LTST-C190CKT	Diode, LED, Red, 2.1-V, 20-mA, 6-mcd	0603	LTST-C190CKT	Lite On
2	D3, D4	LTST-C190GKT	Diode, LED, Green, 2.1-V, 20-mA, 6-mcd	0603	LTST-C190GKT	Lite On
2	D5, D6	MBRS1100	Diode, Schottky, 100 V, 1 A	SMB	MBRS1100T3G	On Semi
1	D7	SMCJ43A	TVS 1500-W 43-V UNIDIRECTIONAL	SMC	SMCJ43A	Diodes
4	D8, D20, D25, D27	MMSZ5222BT3 G/2.5 V	Diode, Zener, 2.5 V, 20 mA	SOD123	MMSZ5222BT1G	On Semi
2	D9, D10	STTH5R06B	Diode, Ultra-Fast High-Power Rectifier, 600 V, 5 A	DPAK	STTH5R06B-TR	ST
4	HS1, HS2, HS3, HS4	531002B02500G	Heatsink, TO-220, Vertical-mount with Solderable pins	0.5 × 1.38 in	531002B02500G	Aavid
4	J1, J3, J4, J11	ED120/2DS	Terminal Block, 2-pin, 15 A, 5,1 mm	0.4 × 0.35 in	ED120/2DS	OST
1	J10	923345-04-C	Jumper, 0.400-in length, PVC Insulation, AWG 22,	0.035-in Dia.	923345-04-C	3M
2	J2, J5	PEC03SAAN	Header, Male 3-pin, 100-mil spacing,	0.1 × 3 in	PEC03SAAN	Sullins
1	J6	182-009-212-171	Connector, 9-pin D, Right Angle, Female	1.213 × 0.51	182-009-213R171	Norcomp
1	J7	PEC03DAAN	Header, Male 2- x 3-pin, 100 mil spacing	0.2 × 0.3 in	PEC03DAAN	Sullins
1	J8	131-4244-00	Adaptor, 3,5-mm probe clip (or 131-5031-00)	0.2 in	131-4244-00	Tektronix
1	J9	8021	Jumper, 1.2-in length, Solid Tinned Copper, AWG 22, Noninsulated	AWG 22	8021	Belden
1	L1	2.2 µH	Inductor, 1.83 mΩ, 100 A	1.1 × 1.1 in	SER2814H-222KL	Coilcraft
1	L2	22 µH	Inductor, 1.83 mΩ, 100 A	.863 × .453 in	PCH-45X-223_LT	Coilcraft
2	P1, P2	87758-4016	Header, 40-pin, 2-mm Pitch	4 × 40 mm	87758-4016	Molex
1	P3	PEC08DAAN	Header, Male 2- x 8-pin, 100-mil spacing	.1 in X2X8	PEC08DAAN	Sullins
0						
0	Q1, Q2, Q4, Q8	Open	MOSFET, Nch, 25 V, 220 mA, 5 Ω	SOT23	FDV301N	Fairchild
0 3	Q1, Q2, Q4, Q8 Q3, Q5, Q9	Open MMBT3904LT1G	MOSFET, Nch, 25 V, 220 mA, 5 Ω Trans, NPN, 40 V, 20 0mA, 225 mW	SOT23 SOT23	FDV301N MMBT3904LT1G	Fairchild On Semi
						On Semi
3	Q3, Q5, Q9	MMBT3904LT1G	Trans, NPN, 40 V, 20 0mA, 225 mW	SOT23	MMBT3904LT1G	On Semi
3 2	Q3, Q5, Q9 Q6, Q10	MMBT3904LT1G SI7866ADP	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ	SOT23 PWRPAK S0-8	MMBT3904LT1G SI7866ADP-T1-E3	On Semi Vishay-Siliconix
3 2 1	Q3, Q5, Q9 Q6, Q10 Q7	MMBT3904LT1G SI7866ADP MMDT3946	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW	SOT23 PWRPAK S0-8 SC-70 (SOT-363)	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F	On Semi Vishay-Siliconix Diodes
3 2 1 2	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2,	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50	On Semi Vishay-Siliconix Diodes STM
3 2 1 2 4	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS	On Semi Vishay-Siliconix Diodes STM TI
3 2 1 2 4 2	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50	On Semi Vishay-Siliconix Diodes STM TI STM
3 2 1 2 4 2 4	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD	On Semi Vishay-Siliconix Diodes STM TI STM STD
3 2 1 2 4 2 4 1	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805 0603	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD STD	On Semi Vishay-Siliconix Diodes STM TI STM STD STD STD
3 2 1 2 4 2 4 1 2	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, ½ W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805 0603 1210	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STM STD STD STD STD
3 2 1 2 4 2 4 1 2 2 2 2	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/8 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805 0603 1210 0805	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STM STD STD STD STD STD STD
3 2 1 2 4 2 4 1 2 2 2 1	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, ½ W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/8 W	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805 0805 0805	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STD STD STD STD STD STD STD STD
3 2 1 2 4 2 4 1 2 2 1 0 1	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R15, R16, R44, R87,	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0 Open	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/16 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805 0603 1210 0805 0805 0805 0603	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STD12NM50 STD STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STM STD STD STD STD STD STD STD STD
3 2 1 2 4 2 4 1 2 2 1 0 1	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R18, R24, R26, R37, R39, R42, R48, R58, R51, R64, R65, R66,	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0 Open 35k	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/8 W Resistor, Chip, 1/16 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220 TO-220V 0805 0603 1210 0805 0603 0603 0603 0603	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD STD STD STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STD
3 2 1 2 4 2 4 1 2 2 1 0 1 1 5	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R55, R16, R44, R55, R102 R15, R102 R15, R16, R44, R55, R16, R46, R56, R16, R16, R16, R16, R16, R16, R16, R1	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0 Open 35k 10.0k	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220V 0805 0603 1210 0805 0603 0603 0603 0603 0603 0603	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STP12NM50 STD STD STD STD STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STD
3 2 1 2 4 2 4 1 2 2 1 0 1 1 5 2	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R19, R32	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0 Open 35k 10.0k 0	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220V 0805 0603 0603 0603 0603 0603 0603 0603 0603 1210 0805 0603 1210 0603 1210 0603 1206	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STD12NM50 STD STD STD STD STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STD STD
3 2 1 2 4 2 4 1 2 2 1 2 1 0 1 1 5 2 4	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R16, R64, R65, R66, R88, R90, R92 R19, R32 R2, R4, R9, R35	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0 Open 35k 10.0k 0 2.43	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220V 0805 0603 0603 0603 0603 0603 0603 0603 1210 0603 1210 1206	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STD STD STD STD STD STD STD STD STD ST	On Semi Vishay-Siliconix Diodes STM TI STD
3 2 1 2 4 2 4 1 2 2 1 0 1 1 5 2 4 2	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R18, R24, R26, R37, R39, R42, R48, R58, R61, R64, R65, R66, R88, R90, R92 R19, R32 R2, R4, R9, R35 R20, R21	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 51.1 10 0 Open 35k 10.0k 0 2.43 15.0k	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, ½ W, 1% Resistor, Chip, ½ W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220V 0805 0603 0603 0603 0603 0603 1210 0603 0603 1206 1206 1210	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STD12NM50 STD STD STD STD STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STD STD
3 2 1 2 4 2 4 1 2 2 1 0 1 1 5 2 4 2 1	Q3, Q5, Q9 Q6, Q10 Q7 QB1, QB2 QSYN1, QSYN2, QSYN3, QSYN4 QT1, QT2 R1, R3, R8, R10 R103 R11, R12 R13, R40 R14 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R15, R16, R44, R87, R102 R18, R24, R26, R37, R39, R42, R48, R58, R61, R64, R65, R66, R88, R90, R92 R19, R32 R2, R4, R9, R35 R20, R21 R22	MMBT3904LT1G SI7866ADP MMDT3946 STP12NM50 CSD18532KCS STP12NM50 5.11k 5.11k 5.11k 51.1 10 0 Open 35k 10.0k 0 2.43 15.0k 0.5	Trans, NPN, 40 V, 20 0mA, 225 mW MOSFET, NCh, 20 V, 40 A, 3 mΩ Transistor, Dual NPN, 60V, 200mA, 200mW MOSFET, N-ch, 550-V, 12-A, 0.35-ohms NexFET, N-ch, 60V, 100A, 3.3milliohm MOSFET, N-ch, 550-V, 12-A, 0.35-ohms Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, 1/8 W, 1% Resistor, Chip, 1/16 W, 1% Resistor, Chip, ½ W, 1% Resistor, Chip, ½ W, 1% Resistor, Chip, ½ W, 1%	SOT23 PWRPAK S0-8 SC-70 (SOT-363) TO-220V TO-220V 0805 0603 0603 0603 0603 1206 1210 0603 0603	MMBT3904LT1G SI7866ADP-T1-E3 MMDT3946-7-F STP12NM50 CSD18532KCS STD12NM50 STD STD STD STD STD STD STD STD STD STD	On Semi Vishay-Siliconix Diodes STM TI STD

Table 4. Component List Based on the Schematics of Figure 1 and Figure 2⁽¹⁾ (continued)

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QTY	RefDes	Value	Description	Size	Part Number	MFR
0	R29, R72, R73	Open	Resistor, Chip, ¼ W, 1%	1206	STD	STD
2	R30, R76	0	Resistor, Chip, 1/10 W	0603	STD	STD
5	R31, R56, R59, R62, R75	3.32k	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
1	R33	1.00k	Resistor, Chip, ¼ W, 1%	1206	STD	STD
1	R38	549	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
3	R41, R45, R101	100k	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
4	R49, R50, R51, R52	1.12k	Resistor, Chip, ¼ W, 1%	1206	STD	STD
2	R5, R34	100	Resistor, Chip, 1/10 W, 1%	0805	STD	STD
3	R53, R104, R105	0.003	Resistor, 1 W, 1%	1210	STD	STD
2	R54, R55	15	Resistor, Chip, 1/8 W, 1%	0805	STD	STD
3	R57, R60, R63	301	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
4	R6, R7, R36, R46	7.5	Resistor, Chip, ¼ W, 1%	1206	STD	STD
4	R67, R68, R84, R85	1.00k	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
1	R69	49.9k	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
1	R74	2.00k	Resistor, Chip, 1/16 W, 1%	0603	STD	STD
1	R77	2.05k	Resistor, Chip, 1/16W, 1%	0603	STD	STD
1	R78	1.24k	Resistor, Chip, 1/10W, 1%	0603	STD	STD
3	R79, R82, R97	16.2k	Resistor, Chip, 1/16W, 1%	0603	STD	STD
3	R80, R83, R98	1.82k	Resistor, Chip, 1/16W, 1%	0603	STD	STD
2	R81, R86	499	Resistor, Chip, 1/8W, 1%	0805	STD	STD
1	R89	4.99k	Resistor, Chip, 1/16W, 1%	0603	STD	STD
1	R91	220	Resistor, Chip, 1/10W, 1%	0603	STD	STD
2	R93, R100	1.0k	Resistor, Chip, 1/2W,1%	1210	STD	STD
3	R94, R95, R96	549	Resistor, Chip, 1/4W, 1%	1206	STD	STD
1	R99	1.62k	Resistor, Chip, 1/16W, 1%	0603	STD	STD
1	S1	G12AP-RO	Switch, ON-NONE-ON	0.28 × 0.18 in	G12AP-RO	NKK
1	T1	1.2 mH	Transformer, Phase Shifted Full Bridge	35,5 × 39,1 mm	7840-08-0015	Nova Magnetics Inc
1	T2	80 mH	Transformer, Current Sense, 1:200	0.57 × 0.77 in	CS4200V-01L	Coilcraft
2	T3, T4	460 µH	Transformer, Gate Drive, ±25%	0.685 × 0.95 in	GA3550-BL	Coilcraft
1	U1	TPS2411PW	IC, N+1 and Oring Power Rail Controller	TSSOP-14	TPS2411PW	TI
1	U10	LM60C	IC, 2.7V Temperature Sensor	SOT23	LM60CIM3/NOPB	ТІ
1	U2	OPA345NA	IC, R-R Op Amp, Single Supply,	SOT23-5	OPA345NA/250	ті
4	U3, U4, U5, U8	UCC27424DGN	IC, Dual Non-Inverting 4A High Speed Low-Side MOSFET Driver w/ Enable	HTSSOP	UCC27424DGN	ті
1	U6	PWR050 ⁽²⁾	Module, 5W, Auxiliary Bias PS	1.2 × 2.2 in	PWR050	ті
1	U7	SN75C3221	IC, RS-232 Transceivers with Auto Shutdown	SSOP-16	SN75C3221DBR	TI
1	U9	TPS715A33	IC LDO REG	QFN-8	TPS715A33DRBT	TI
1	U11	PWR030	Control Card, UCD3138 control card, PCB assembly	3.4 × 1.8 in	UCD3138CC64EVM-030	TI

Table 4. Component List Based on the Schematics of Figure 1 and Figure 2⁽¹⁾ (continued)

⁽²⁾ PWR050 is a bias board and the design documents are found in the UCD3138PSFBEVM-027 product folder on <u>www.ti.com</u>.

12 Description of the Digital Phase-Shifted Full-Bridge Converter

12.1 Block Diagram of the Phase-Shifted Full-Bridge Converter

Figure 22 shows the block diagram of the phase-shifted full-bridge converter used in the EVM. The signals used for control and for detection are defined in Section 12.2 in connection with the UCD3138 pins.

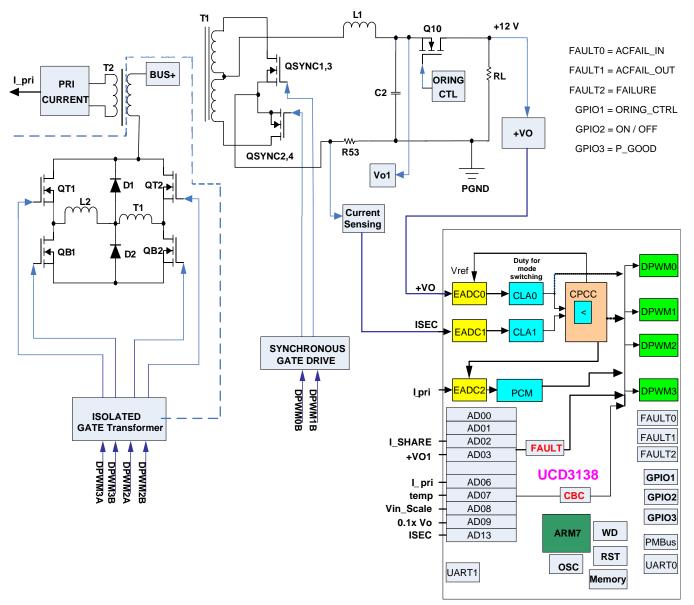


Figure 22. Phase-Shifted Full-Bridge Converter Block Diagram

12.2 UCD3138 Pin Definitions

The UCD3138 pins are defined according to Figure 23. The definitions shown in Figure 23 are for the pins used in the EVM to control a phase-shifted full-bridge converter. See Figure 21 for how the signals on these pin signals are used.

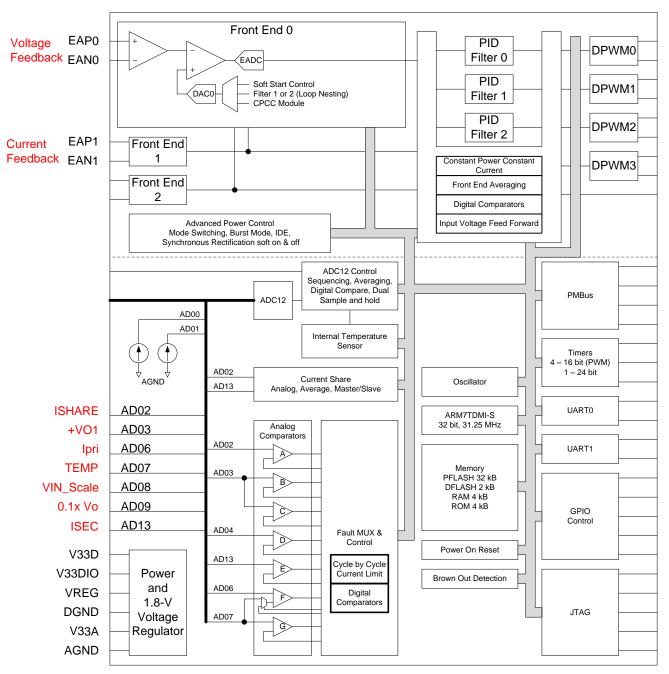


Figure 23. UCD3138 Pin Definition in Phase-Shifted Full-Bridge Control



12.3 EVM Hardware — Introduction

This section describes the EVM hardware functions.

12.3.1 Power Stage

This EVM implements topology for a phase-shifted full-bridge DC-DC converter. The key waveforms generated by the UCD3138 to control the phased-shifted power stage are shown in Figure 24. See Section 4 for the complete schematics. On the primary side, QT1, QB1, QT2, and QB2 are the power switches, L2 is a resonant inductor (often called *shim* inductor), and T1 is the main transformer. D9 and D10 are clamping diodes. T2 is a current transformer for sensing primary-side current and is located on the high side. T5 is not used and is shorted by jumper J10.

The secondary side is configured as a central-tap synchronous rectifier comprised of an output choke (L1), output capacitor (C4 and C62), and synchronous MOSFETS (QSYN1, QSYN2, QSYN3 and QSYN4). Q6 and Q10 are oring FETS for hot swap. T3 and T4 are gate transformers to drive primary-side power MOSFETs and provide isolation boundary. Two gate drivers (U4 and U5) are used for driving the gate transformers. Two low-side drivers, U3 and U8, are used for driving the secondary-side synchronous MOSFETs.

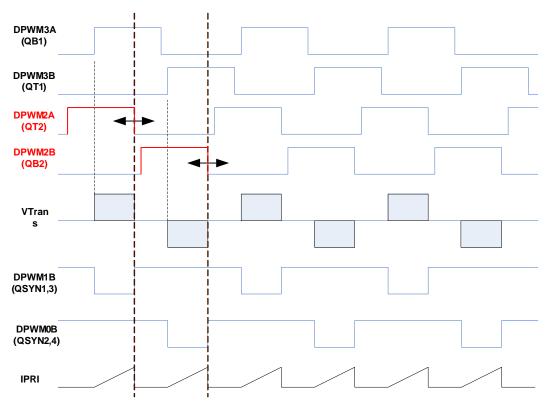


Figure 24. Driving Scheme of Phase-Shifted Full-Bridge Control

The following lists the DPWM configuration for the phase-shift full bridge converter:

DPWM3A to VGS_QB1 DPWM2A to VGS_QT2 DPWM1B to VGS_QSYN2 and QGS_QSYN4 DPWM3B to VGS_QT1 DPWM2B to VGS_QB2 DPWM0B to VGS_QSYN1 and QGS_QSYN3

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When both QB1 and QT2 turn on, the input voltage Vbus is applied to the power transformer and energy is transferred to the output. During this period, QSYN1 and QSYN3 are turned off and power is transferred through L1 to the output. The return current flows through QSYN2 and QSYN4, which are turned on, and then the current flows back to the secondary side of the main transformer. When QB2 and QT1 are both on, the bus voltage is applied to the power transformer in the opposite direction. In this case, QSYN2 and QSYN4 are turned off and power is transferred through L1 to the output. The return current flows through QSYN4 are turned off and power is transferred through L1 to the output. The return current flows through QSYN1 and QSYN3, which are turned on, and then flows back to the main transformer. When all four switches on the primary side are turned off, the secondary side works in a freewheeling mode, meaning all sync FETs are turned on and the inductor current flows through the switches. See Section 15 for a list of references containing additional details about the phase-shift full-bridge converter.

Because the digital controller generating the six DPWMs in on the secondary side and four of the power switches are on the primary side, the converter requires an isolation component to cross the boundary. Pulse transformers, T3 and T4, transmit the gate signal and drive the primary-side power MOSFETs. These transformers are used because they are simple and low cost although they typically require more space than digital isolators. Two drives, U5 and U6, drive the gate-drive transformers from the secondary side. The leakage inductance of the gate transformer oscillates with other capacitors in the gate-drive circuit during dead time. If the leakage inductance oscillates with other capacitors, a glitch can occur. A negative voltage is provided by the components D20 and C36 for QT1. Other switches use the same circuit that generates negative current. The secondary-side switches do not require isolation. Two ICs, U3 and U8, directly drive these switches.

The dead time between all switches is important to achieve zero-voltage switching based on different operation conditions such as load current and input voltage.

For peak-current-mode control, slope compensation is important to stabilize the loop and avoid the nonperiodic ripple of the output voltage. The slope is generated either internally or externally. If the slope compensation is generated externally, DPWM0A and DPWM1A are used. In this case, install the jumpers between Pin1 to Pin2 and between Pin5 and Pin6 for proper operation. Install Q1, Q2, Q4, and Q8 to generate the slope.

External slope-compensation circuits require many external components. In default, internal slope compensation is used. The controller generates the slope and adds the slope on the filter output of the voltage loop. EAP2 requires a pullup resistor to provide over 100-mV DC offset voltage, which is important to stabilize the loop at the small duty.

12.3.2 Bias Power Supply

The bias supply is a flyback converter using the UCC28600 controller from TI. The bias is an independent daughter-card, the PWR050. The design files (<u>SLUR924</u>) are located in the UCD3138PSFBEVM-027 product folder on <u>www.ti.com</u>. Figure 25 shows the schematic of the PWR050.

There is one 12-V output (PN3-PN4) on the primary side and one 12-V output (PN5-PN7) on the secondary side. The feedback signal is taken from the secondary 12-V output. The controller requires +3.3 V, which is derived from the secondary 12-V output through a LDO regulator (U2).



12.3.3 Sensing Input Voltage on Secondary-Side

In Figure 25 there is sample-and-hold circuit on the secondary side of the PWR050, which senses the primary-side voltage. When the Q2 switch turns on, D5 turns on. The voltage on the winding (6, 7) of the bias transformer T1 charges capacitor C9 to a voltage equal to VIN / N after the divider of R16 and R14, where N is the turns ratio of T1. When Q2 turns off, D5 turns off, and the voltage on C9 is held until the next switching period. The voltage on C9 is proportional to the input voltage. U4 is used to scale the sampled voltage to the application.

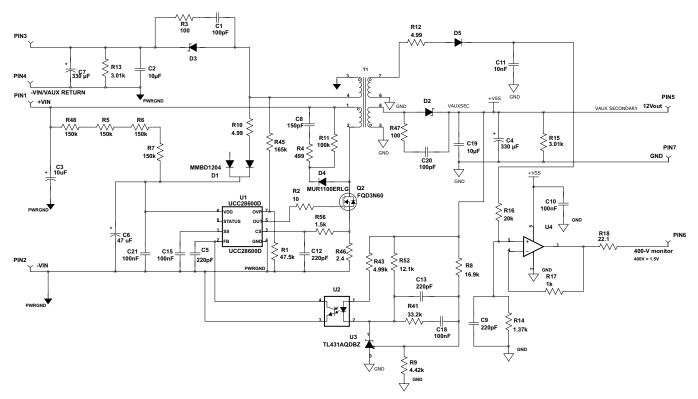


Figure 25. PWR050 Bias Board Schematics

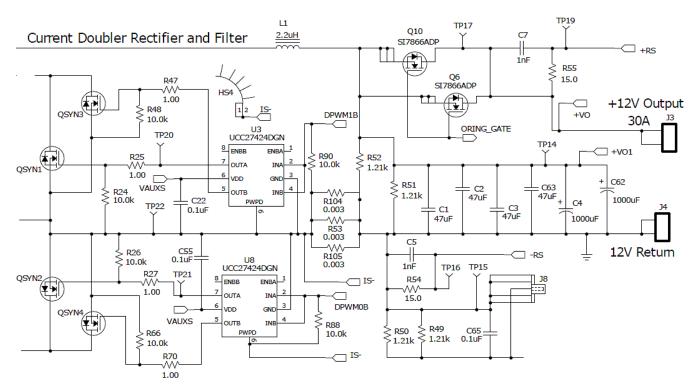


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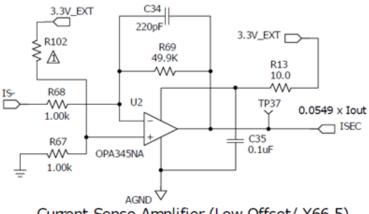
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12.3.4 Load Current Sensing

Figure 26 and Figure 27 show how the load current is sensed and fed back to the UCD3138. A 1-m Ω sense-resistance value (R53 // R104 // R105) senses the load current. A differential amplifier circuit amplifies and filters this signal. The result is supplied to EADC1 and AD13. The sensed current is also used in constant-current and constant-power (CPCC) operation. The AD13 monitors the current. The AD13 also has a mechanism for a fast latch-off over current and the means to implement either masterand-slave or average-mode current sharing.







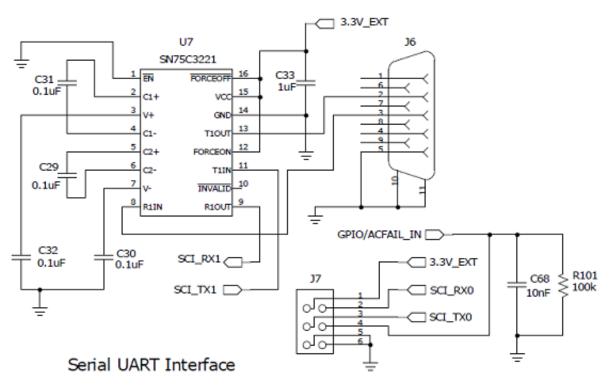
Current Sense Amplifier (Low Offset/ X66.5)

Figure 27. Load-Current-Sensing Conditioning Circuit



12.3.5 Serial Port Interface

The schematic of the interface for the serial port (UART) is shown in Figure 28. The UART provides realtime debug and subsequently reduces code-development time. This serial port also monitors for fastchanging internal variables.





12.3.6 LED Indicators

Table 5. LED Statu	s Lights
--------------------	----------

Ref. Designator	Silk Screen Text	Function
D26	12VP_ON	This LED turns green when 12 V is present on the primary side.
D2	FAILURE	This LED turns red when a fault is detected.
D3	P_GOOD	This LED turns green when the output voltage is within the thresholds defined by PMBUS_CMD_POWER_GOOD_ON and PMBUS_CMD_POWER_GOOD_OFF[1].
D5	AC_P_FAIL_OUT	This LED is not used.

Description of the Digital Phase-Shifted Full-Bridge Converter

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12.3.7 EVM Resource Allocation

The UCD3138PSFBEVM-027 is controlled by a control card, the UCD3138CC64EVM-030, through two 40-pin connectors, P1 and P2. Table 6 lists the definitions of P1 and P2 on the UCD3138PSFBEVM-027 board.

Header Pin No.	UCD3138 Pin Name	Usage Description	
P1-1	DPWM_0A	DPWM0A, slope generation	
P1-2	DPWM_0B	DPWM0B, controls the secondary-sync FET, QSYN1, 3.	
P1-3	DPWM_1A	DPWM1A, slope generation	
P1-4	DPWM_1B	DPWM1B, controls the secondary-sync FET, QSYN2, 4.	
P1-5	DPWM_2A	DPWM2A, controls the primary-side FET, QT2.	
P1-6	DPWM_2B	DPWM2B, controls the primary-side FET, QB2.	
P1-7	DPWM_3A	DPWM3A, controls the primary-side FET, QB1.	
P1-8	DPWM_3B	DPWM3B, controls the primary-side FET, QT1.	
P1-9	DGND	Digital ground (GND)	
P1-10	DGND	Digital ground (GND)	
P1-11	GPIO08	ON/OFF	
P1-12	GPIO09/FLT1B	GPIO_ORING_CTR	
P1-13	GPIO10	Failure	
P1-14	GPIO11/FLT2B	P_GOOD	
P1-15	GPIO28	Not used	
P1-16	GPIO29	Not used	
P1-17	GPIO30	Not used	
P1-18	GPIO31	Not used	
P1-19	GPIO32/FLT4A	I_FAULT	
P1-20	GPIO33/ FLT4B	LATCH_ENABLE	
P1-21	GPIO26	Not used	
P1-22	GPIO22	Not used	
P1-23	GPIO24	Not used	
P1-24	GPIO23	Not used	
P1-25	GPIO18/PWM1	AC_FAIL	
P1-26	GPIO19/PWM2	ACFAILIN	
P1-27	GPIO20	Not used	
P1-28	GPIO21	Not used	
P1-29	GPIO34	Not used	
P1-30	GPIO35	Not used	
P1-31	GPIO16/SCI_TX	SCI transmit	
P1-32	GPIO17/SCI_RX	SCI receive	
P1-33	GPIO25	Not used	
P1-34	GPIO27	Not used	
P1-35	GPIO27	Not used	
P1-36	RESET*	Not used	
P1-37	DGND	Digital ground (GND)	
P1-38	DGND	Digital ground (GND)	
P1-39	VauxS	External 12-V DC supply	
P1-40	Not connected to UCD3040	Not used	
P2-01	AGND	Analog ground (GND)	
P2-02	ADCREFin	Not used	

Table 6. P1 and P2 Pin Assignment



Header Pin No.	UCD3138 Pin Name	Usage Description	
P2-03	AGND	Analog ground (GND)	
P2-04	AD_00	PMBus ADDR	
P2-05	AGND	Analog ground (GND)	
P2-06	AD_01	PMBus ADDR	
P2-07	AGND	Analog ground (GND)	
P2-08	AD_02	AD_02, output current sensing	
P2-09	AGND	Analog ground (GND)	
P2-10	AD_03	AD_03, primary current sensing	
P2-11	AGND	Analog ground (GND)	
P2-12	AD_04	AD_04, current-sharing bus sensing	
P2-13	AGND	Analog ground (GND)	
P2-14	AD_05	AD_05, inside-oring FETs voltage sensing	
P2-15	AGND	Analog ground (GND)	
P2-16	AD_06	AD_06, outside-oring FETs voltage sensing	
P2-17	AGND	Analog ground (GND)	
P2-18	AD_07	AD_07, temperature sensing	
P2-19	AGND	Analog ground (GND)	
P2-20	AD_08	AD_08, VINSCALED sensing	
P2-21	AGND	Analog ground (GND)	
P2-22	AD_09	I_SHARE	
P2-23	AGND	Analog ground (GND)	
P2-24	AD_10	Not used	
P2-25	AGND	Analog ground (GND)	
P2-26	AD_11	Not used	
P2-27	AGND	Analog ground (GND)	
P2-28	AD_12	Not used	
P2-29	AGND	Analog ground (GND)	
P2-30	AD_13	Not used	
P2-31	AGND	Analog ground (GND)	
P2-32	AD_14	Not used	
P2-33	EAN4	Analog ground (GND)	
P2-34	EAP4	I_PRI	
P2-35	EAN3	Analog ground (GND)	
P2-36	EAP3	Output voltage sensing, or I_PRI	
P2-37	EAN2	Analog ground (GND)	
P2-38	EAP2	Output current sensing	
P2-39	EAN1	Analog ground GND2 (-RS)	
P2-40	EAP1	Output voltage sensing (+RS)	

Table 6. P1 and P2 Pin Assignment (continued)



12.4 EVM Firmware — Introduction

The reference firmware that is provided with the EVM is intended to demonstrate basic phase-shifted fullbridge DC-DC converter functionality, as well as some basic PMBus communication and primary-tosecondary communication. The firmware is used as an initial platform for particular applications. This section provides a brief introduction to the firmware.

12.4.1 Firmware Infrastructure overview

The firmware includes one startup routine and three program threads. The startup routine initializes the controller setup for the targeted operation functions or status. Please contact TI for detailed initialization information.

As shown in Figure 34, the three program threads are (1) the fast-interrupt request (FIQ); (2) the timerinterrupt request (IRQ); and (3) the background loop. These threads are described as:

- 1. Fast Interrupt (FIQ)
 - Critical or time-sensitive tasks are within the FIQ. Functionally, FIQ events are the highest priority and are addressed as soon as possible.
- 2. Timer Interrupt (IRQ)
 - The majority of the firmware tasks occur during the IRQ. IRQ events occur synchronously every 100 $\mu s.$
- 3. Background Loop
 - Non time-sensitive tasks are implemented in the background loop. Background Loop items are addressed whenever FIQ and IRQ events are not handled.

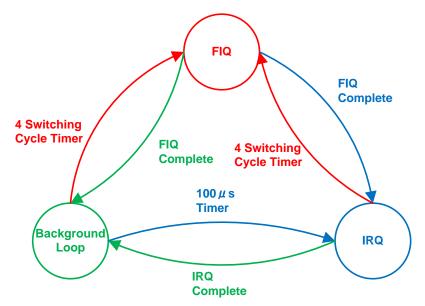


Figure 29. Firmware Structure Overview

12.4.2 Tasks Within FIQ

FIQ events have the highest priority and are addressed as soon as possible. The FIQ includes critical and time-sensitive tasks. The firmware included with the EVM includes two functions called by the FIQ:

- Constant Power and Constant Current
- Cycle-by-cycle current limit

The FIQ interrupt is called to respond every four switching cycles.



12.4.3 Tasks Within IRQ and State Machine

Almost all firmware tasks occur during the IRQ. The exceptions are the serial interface and PMBus tasks, which occur in the Background Loop; and the overcurrent protection (OCP), which is handled by the FIQ. The IRQ is called to respond every 100 μ s.

At the heart of the IRQ function is the power-supply State Machine implemented with *switch* command. Figure 30 shows the structure of the State Machine. At a higher level, this State Machine allows the digital controller to optimize the performance of the power supply based on the exact State Machine functions of the digital controller.

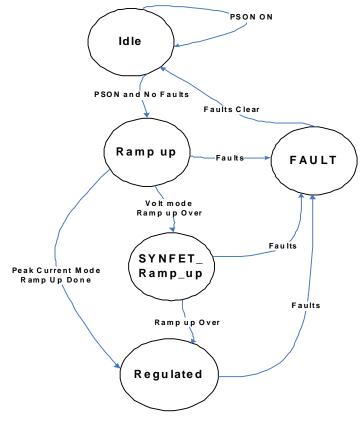


Figure 30. State Machine

12.4.4 Tasks Within Background Loop

The background loop handles all PMBus communication as well as processing and transmitting data through the UART. The data flash is managed with a dual-bank approach. This provides redundancy in the event of a power interruption during the programming of data flash. Once new data-flash values have been written, a function called erase_task() initiates in the background loop to erase the old values. The erase_task() is called until all of the old DFLASH segments are erased. Erasing the data flash in segments allows the processor to handle other tasks instead of waiting for the entire data flash to be erased before completing other tasks.

12.4.5 System Normal Operation

The EVM is designed to operate in peak-current-mode control under normal operation conditions. The EVM operates with output voltage in regulation across the load range. If the load power continues to increase beyond the rated value, then an overload condition occurs. In such a case, the system enters protection operation by entering CPCC mode. If load power still continues to increase, output shutdown is triggered.

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12.4.5.1 Peak-Current-Mode Control

Peak-current-mode control is used in this EVM. The primary-side peak current is used to create control, and is sensed through current transformer T2. The slope compensation is realized within the digital-controller internal setup which is re-programmable to adapt to required applications. External slope compensation is also used with component place-holders in place. Please contact TI for information on how to re-program the internal slope compensation and how to set up the external slope compensation.

12.4.5.2 Other Possible Control Modes

Voltage-Mode Control and Average Current-Mode Control are also possible. To change the EVM into these controls, both hardware and firmware require modifications. Please contact TI for more information on how to make these modifications.

12.4.6 System Operation in Protection

12.4.6.1 Faults and Warnings

The system is equipped with a variety of programmable fault and warning options. Table 5 lists the LEDs used to indicate a fault. Table 7 lists the basic faults and warnings available in the EVM along with the corresponding action required by these events. Each of these parameters is modified through the GUI.

Signal	Туре	Warning	Fault Response
VOUT	Over	Report	Report and latch off
	Under	Report	Report
VIN	Over	Report	Report and latch off
VIIN	Under	Report	Report and latch off
IOUT	Over	Report	Report and latch off
IIN	Over	Report	Cycle-by-cycle limiting
SR (QSYN3) Temperature	Over	Report	Report and latch off

Table 7. Faults and Warnings



Description of the Digital Phase-Shifted Full-Bridge Converter

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Reporting a fault includes the appropriate setting of the PMBus alert line, status byte, and status word. Faults and warnings are reset by toggling the unit off and then on. Alternatively, as long as the system does not latch off, the *Clear Faults* button clears any faults or warnings (see Figure 31). Faults and warnings are also cleared by toggling the control line the on-off switch.

Status Registers/Lines			
Vout:	ок		
Iout:	ОК		
Temp:	ОК		
Input:	ОК		
CML:	ОК		
Misc:	Output Off, POWER_GOOD#		
Debug Buffer:	0x0102030405060708		
Mfr:	ОК		
SMBALERT#	Not Asserted		
Clear Faults			

Figure 31. Faults and Warnings

12.4.6.2 Cycle-By-Cycle Current Limit

Current transformer T2 senses the primary-side current. Figure 32 shows the sensing circuit. This current is used for cycle-by-cycle current limit, peak-current-mode control, or flux balancing of the main transformer. The primary-peak current is limited within the primary MOSFET current ratings by the cycle-by-cycle current limit. R31 and C17 are used as a low-pass filter before the current signal feeds to the UCD3138. The current signal is sent into UCD3138 through AD06 to create cycle-by-cycle current-limit control. To prevent switching spikes from triggering the comparator, a blanking time is programmed.

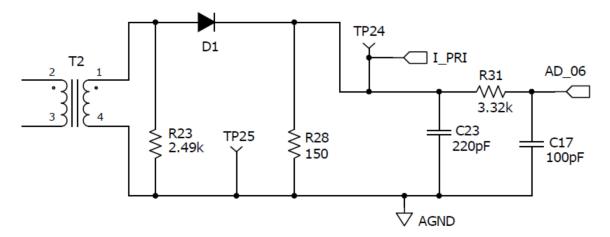


Figure 32. Cycle-by-cycle Current-Limit Sensing Circuit



12.4.6.3 Constant Power and Constant Current Operation

Both hardware and firmware in this EVM support CPCC operation. Figure 33 illustrates the behavior of the output voltage and output current (V_{OUT} versus I_{OUT}). The dashed lines represent an extended view.

The EVM is delivered already programmed with a constant-power threshold of a few watts over 360 W and a constant-current threshold of 33 A (typical). These limits are adjustable through the GUI and a new setting can be saved to data flash. The maximum hardware capability limits the current within 35 A. The dashed lines represent exceeding the constant power to a higher current, although the maximum current of this EVM is limited to 35 A. Figure 34 shows the GUI default values of these controls.

In addition to setting the previously described thresholds, enabling or disabling the CPCC feature and configuring a fault timer is also possible. Whenever the State Machine detects CPCC operation a timer starts. If the timer reaches the time limit specified in Figure 34, the system latches off until the on command toggles off and on again, or recycles the input power.

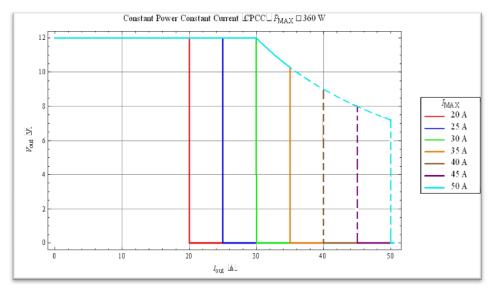


Figure 33. CCPCC Operation

PMAX:	360.0 🔷 W	
IMAX:	35.0 🔪 A	
TON:	10,000.0 🔶 msec	
Enable:	ON 🗸	
Timer:	ON 🗸	
×		:

Figure 34. CPCC Default Values Adjusted Through GUI



12.4.6.4 Output Over Voltage

When the output voltage exceeds 15.6 V, Q7-B turns on then Q7-A turns on because the Q7-A base is low. OVP_LATCH is pulled low, which is detected by the controller. The output voltage is shut down and latched. Figure 35 shows the circuit.

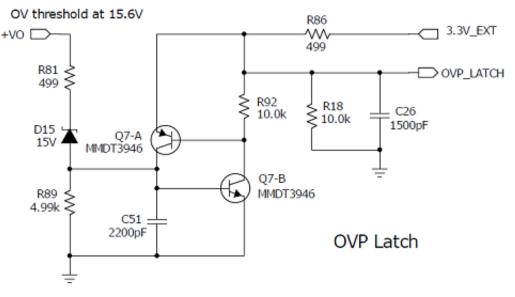


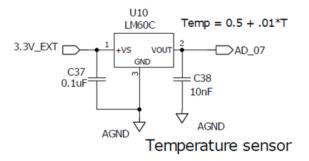
Figure 35. Redundant-Output Overvoltage Protection

12.4.6.5 Input Over Voltage

The input over voltage is detected based on the winding on the auxiliary power supply as described in Section 12.3.3. The detected signal is sent to AD08 to create a fault process.

12.4.6.6 Over Temperature

Over temperature includes UCD3138 internal-temperature sensing and external added-temperature sensing. A temperature-sensing element on U10, LM60C, determines the external overtemperature condition. The temperature signal feeds into the controller through AD07. U10 is located on the top-side of the board next to the QSYNC3 heat sink. At this location U10 senses the temperature of the secondary-side MOSFETs.





12.5 Special Operation Modes

12.5.1 Light Load Operation

At light load, the burst operation enables when the switching duty cycle is small. The significant benefit of this operation is the reduction of power loss. The associated disadvantage is higher output voltage-ripple and larger output voltage-dip when the load has a sudden demand. But the higher ripple and the larger dip disadvantages are corrected by the convenience and flexibility of the digital control. For example, non-linear control from digital control solves the large dip during load transient. The higher ripple is also reduced by narrowed duty cycle on and off-limit for burst operation control. Figure 37 shows the burst operation timing diagram.

NOTE: The burst operation mode is still in development for this EVM. Please contact TI for the latest development information.

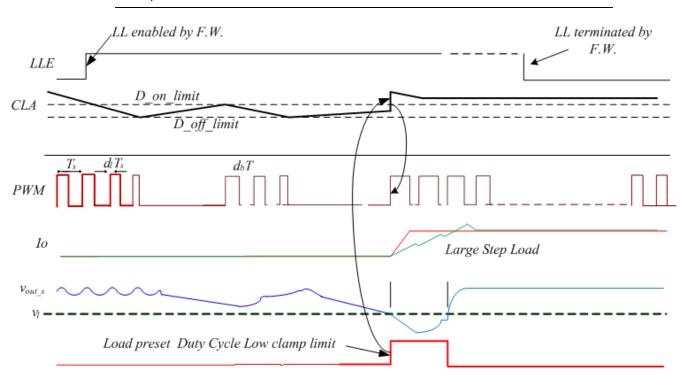


Figure 37. Burst Operation Timing Diagram



12.5.2 Current-Sharing Operation

The UCD3138 supports three major current-sharing techniques:

- Average current-sharing, or PWMbus current-sharing
- Master and slave current-sharing
- Droop-Mode Current-Sharing, or Analog bus current-sharing

This EVM uses average current-sharing. The average-current-sharing technique uses a share bus to balance and evenly distribute the current on each paralleled converter as shown in Figure 38. The share bus is called ISHARE in this EVM design. Therfore, when making load current sharing, ISHARE from each board must be connected together. ISHARE connection is located on J2 terminal pin 3 and through R91 and C12 fed into AD02. The load current is connected to AD13 after a low-pass filter (R85 and C49) from ISEC. The current-sharing module is integrated in the UCD3138, and the ISHARE bus is controlled properly by UCD3138 internal functions.

This current-sharing-operation feature is used for normal operation in steady state with average-currentsharing approach. In CPCC, the current sharing is inherently valid and does not rely on the averagecurrent-sharing approach. This feature is not available during start, burst operation, or cycle-by-cycle current limit.

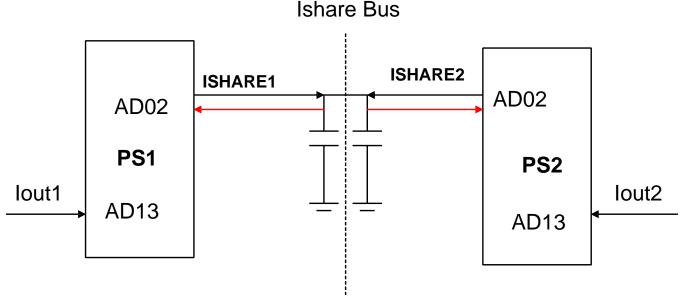


Figure 38. Current-Sharing Operation



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12.5.3 Oring FETs Control

The oring control circuit is shown in Figure 39. Q6 and Q10 are oring FETs used for hot-swapping operation. Less power-conduction loss occurs when using oring MOSFETs instead of oring diodes. The oring MOSFETs are controlled by the oring-control IC U1, TPS2411. By sensing the voltage between the drain and source of the oring FETs, U1 quickly turns off the oring FETs to avoid reverse current drawn from the output voltage bus. Pull down the gate-drive signal to turn off oring FETs by pulling Pin5 high, which is controlled by the UCD3138. Through output voltage remote sensing, the voltage drop on the load wire is compensated to ensure the voltage at the load point is accurate. +RS and –RS are connected to +VO and 12V_RETURN through the resistors, R55 and R54, respectively.

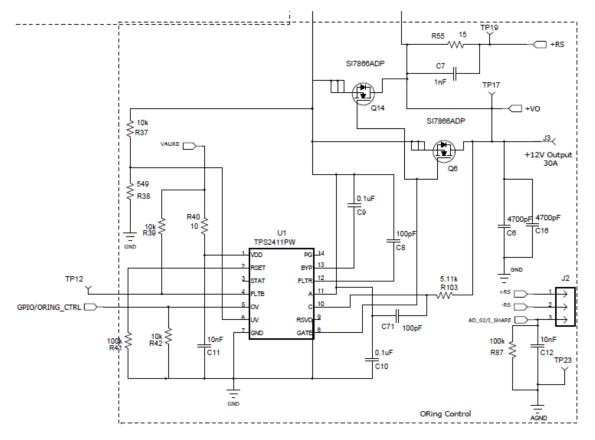


Figure 39. Oring Control

12.6 Loop Compensation Using PID Control

Proportional, integral, and derivative (PID) control is usually used in the feedback-loop compensation in digitally-controlled power converters. This section describes several aspects of how to use PID control.

12.6.1 Transformation of Digital-PID Coefficients to Poles and Zeros in the s-Domain

PID control in the UCD3138 control-law algorithm (CLA) for control loop is formed in the z-domain using Equation 1.

$$G_{c}(z) = K_{P} + K_{I} \frac{1 + z^{-1}}{1 - z^{-1}} + K_{D} \frac{1 - z^{-1}}{1 - \alpha \times z^{-1}}$$
(1)

Converting Equation 1 to the s-domain equivalent using the bilinear transform results in two forms. One form is with two real zeros and one real pole as shown in Equation 2.

$$G_{cz}(s) = K_0 \frac{\left(\frac{\omega_{z1}}{\omega_{z1}} + 1\right)\left(\frac{\omega_{z2}}{\omega_{z2}} + 1\right)}{s\left(\frac{s}{\omega_{p1}} + 1\right)}$$

(s)(s)

 K_0 is the gain of the frequency domain pole at the origin, and K_0 is also represented as the angular frequency when the integrator Bode-plot gain crosses over with 0 dB. K_0 is also used as a method for initially designing feedback-loop compensation (see reference 5 in Section 15 for more details).

The second form is when the two zeros are presented with complex conjugates as shown in Equation 3.

$$G_{cz}(s) = K_0 \frac{\left(\frac{s^2}{\omega_r^2} + \frac{s}{Q \times \omega_r} + 1\right)}{s\left(\frac{s}{\omega_{p1}} + 1\right)}$$
(3)

Two complex conjugate zeros are expressed as,

$$\omega_{z1, z2} = \frac{\omega_r}{2 \times Q} \left(1 \pm j \sqrt{4 \times Q^2 - 1} \right) \quad \text{and} \quad j = \sqrt{-1}$$
(4)

$$\omega_{\rm r} = \sqrt{\omega_{\rm Z1} \times \omega_{\rm Z2}} \tag{5}$$

$$Q = \frac{\sqrt{\omega_{z1} \times \omega_{z2}}}{\omega_{z1} + \omega_{z2}}$$
(6)

The factor of Q is in the range of 0 to infinite. The two complex conjugate zeros become the two real zeros when Q is less than or equal to 0.5 ($Q \le 0.5$). Therefore, Equation 2 is a unique form of Equation 3. In this sense, Equation 3 can be used in either case across the range of Q.

A low-pass filter usually exists in a control loop of its feedback path. The low-pass filter adds a pole to the loop as shown in Equation 7.

$$H_{cs}(s) = K_{cs} \frac{1}{\frac{s}{\omega_{pcs}} + 1}$$
(7)

. ,

(2)



The close-loop transfer function is shown in Equation 8.

$$G_{cs}(s) = \frac{G_{M}(s) \times G_{PID}(s)}{1 + G_{M}(s) \times G_{PID}(s) \times H_{cs}(s)}$$

where

• GM(s) is the control plant transfer function (8)

For example, GM(s) is the transfer function associated to the phase-shifted full-bridge power-modulator circuit.

The parameters are calculated with the assumption that the sensor-sampling cycle, T_s , is much smaller than the time constant in relation to the converter-voltage feedback-loop bandwidth, TLC. As a general rule, choose the sampling frequency as shown in Equation 9.

$$T_{s} \leq 0.05 \times T_{LC}$$
⁽⁹⁾

When the above assumption is true, the delayed effect from the sampling is ignored and the parameters are determined after the position of the poles and zeros is known. Table 8 summarizes the poles and zeros in a form relating the z-domain to the s-domain.

$$K_{P} = \frac{K_{0} \times \left(\omega_{p1} \times \omega_{z1} + \omega_{p1} \times \omega_{z2} - \omega_{z1} \times \omega_{z2}\right)}{\omega_{p1} \times \omega_{z1} \times \omega_{z2}}$$
(10)

$$K_{I} = \frac{K_{0} \times T_{s}}{2}$$
(11)

$$K_{D} = \frac{2 \times K_{0} \times \left(\omega_{p1} - \omega_{z1}\right) \times \left(\omega_{p1} - \omega_{z2}\right)}{\omega_{p1} \times \omega_{z1} \times \omega_{z2} \left(T_{s} \times \omega_{p1} + 2\right)}$$
(12)

$$\alpha = \frac{2 - T_s \times \omega_{p1}}{2 + T_s \times \omega_{p1}}$$
(13)

Table 8. Poles and Zeros from PID Coefficients

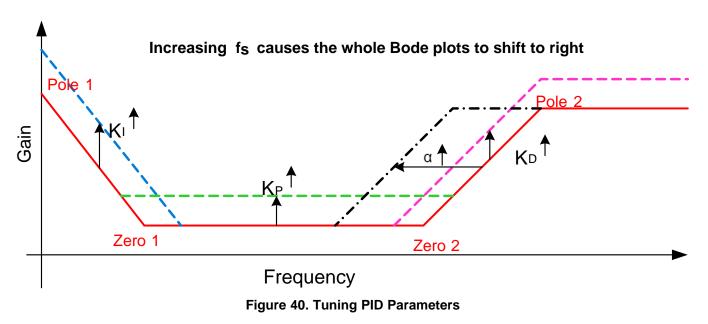
System Name	Transfer Functions
Complex Zeros (K ₀ , f _z , Q _z , f _p)	$\frac{\frac{s^{2}}{(2 \times \pi \times f_{z})^{2}} + \frac{s}{2 \times \pi \times f_{z} \times Q_{z}} + 1}{\frac{s}{2 \times \pi \times K_{0}} \times \left(\frac{s}{2 \times \pi \times f_{p}} + 1\right)}$
Real Zeros (K_0, f_{z1}, f_{z2}, f_p)	$\frac{\left(\frac{s}{2 \times \pi \times f_{z1}} + 1\right) \times \left(\frac{s}{2 \times \pi \times f_{z2}} + 1\right)}{\frac{s}{2 \times \pi \times K_0} \times \left(\frac{s}{2 \times \pi \times f_p} + 1\right)}$
Device PID (K_p, K_i, K_d, α)	$1000 \times \left(K_{p} + K_{i} \times \frac{1 + z^{-1}}{1 - z^{-1}} + K_{d} \times \frac{1 - z^{-1}}{1 - \alpha \times 2^{-8} \times z^{-1}}\right) \times 2^{-sc} \times KCOMP \times 2^{-19} \times \frac{1}{2^{4} \times (PRD + 1)}$



12.6.2 Tuning PID Coefficients for Loop Compensation

When making fine-tuned adjustments to the feedback control loop, knowing how each PID parameter affects the control loop characteristics without using the complicated equations in Table 8 is beneficial. Use Table 9 and Figure 40 as a quick reference for tuning PID coefficients.

Control Parameters	Impact on Bode Plot		
K _p	Increasing $K_{\rm p}$ pushes up the minimum gain between the two zeros, moving the two zeros apart.		
K _i	Increasing K_i pushes up the integration curve at low frequencies, provides a higher low-frequency gain, and moves the first zero to the right.		
K _d	Increasing K_d shifts the second zero left with no impact on the second pole.		
α	Increasing $\boldsymbol{\alpha}$ shifts the second pole and the second zero to the right.		
$T_s = 1 / f_s$	Increasing the sampling frequency f_s shifts the whole Bode plot to the right.		



13 Evaluating the EVM with GUI

The collective graphical user interface (GUI) is called TI's Fusion Digital Power Designer (FDPD). The GUI serves as the interface for several families of TI's digital-control ICs including the UCD31xx family, (such as UCD3138). The GUI is divided into two main categories, Designer GUI and Device GUI. Each UCD31xx EVM relates to a particular Designer GUI allowing users to re-tune and re-configure a particular EVM with existing hardware and firmware. Device GUI relates to the accessing of internal registers and memories of a particular device.

The UCD3138PSFBEVM-027 is used with the UCD3138CC64EVM-030 control card where the UCD3138 device is placed. The firmware for control is loaded onto UCD3138CC64EVM-030 board through the Device GUI. The user's guide, *Using the UCD3138CC64EVM-030* (SLUU886), describes the GUI installation. The Designer GUI is installed at the same time as installing the Device GUI.



13.1 Graphical User Interface (GUI)

As previously mentioned, there are two types of GUI: Device GUI and Designer GUI. The Device GUI is categorized as low-level GUI. From the Device GUI, device registers are accessed if the device is in ROM mode and the PMBus communication is established. This GUI is used to download the code when the device is blank during the initial programming. Also, at the flash mode, a designer can send PMBus commands to read or write the data. The Designer GUI is an interface between a host and a user. It supports some of the PMBus commands to configure, monitor, and design the loop compensator contained in the UCD3138 digital controller.

13.1.1 Hardware Setup

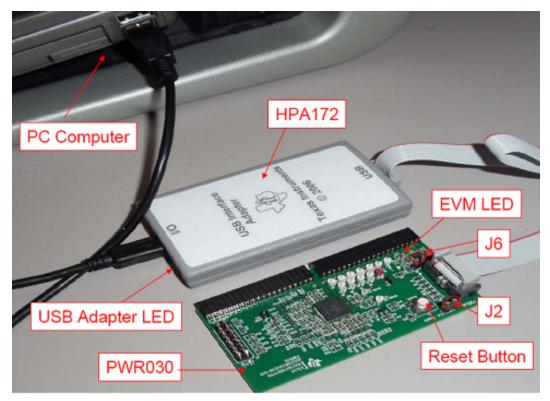


Figure 41. Test Setup

In Section 5.2, Figure 5 and Figure 6 show a basic setup for a power stage test with the EVM. To evaluate the EVM with GUI, the control card must first connect to a GPIO-to-USB adapter card, HPA172, then to a host computer. The following lists the steps for an evaluation:

- 1. Connect the input voltage source to the input connectors shown in Figure 5. Use 14 AWG wire or equivalent.
- 2. Connect the output load to the board. Use a 14-AWG wire or equivalent.
- 3. Plug the control card UCD3138CC64EVM-030 (PWR030) into UCD3138PSFBEVM-027 with the orientation in Figure 5 and Figure 6.
- 4. Confirm that the control card does not have a jumper on J2, and install a jumper on J6.
- 5. Connect the USB-to-GPIO (HPA172) adaptor to the control card as shown in Figure 41, and connect the other end of USB-to-GPIO adapter to the host computer
- 6. Move the ON/OFF control switch, S1, on the phase-shifted full-bridge board, to the OFF position. See Figure 5 to locate S1 on the phase-shifted full-bridge board.
- 7. Configure the load to draw 1 A.
- 8. Apply 380 V to the input with a 2-A current limit set on the input source.



Evaluating the EVM with GUI

- 9. Launch the Fusion Digital Power Designer GUI. See Section 13.1.2 for instructions on how to install the GUI.
- 10. Turn on the board output by switching S1 to the ON position

13.1.2 GUI Installation

Download the GUI software from <u>www.ti.com</u>. Before the GUI is executed, install the software on the host PC. More details about the TI GUI, FDPD, can be found in the user's guide or manual. Please contact TI for the FDPD document. The GUI contains manuals for use with the UCD3138. To find the manuals, use the following sequence:

Help > Documentation and Help Center > UCD3138

Copy over the TI Fusion Digital Power Designer zipped file onto the host computer and unzip the file (*TI-Fusion-Digital-Power-Designer-xx.zip*) to open the installer file, *TI-Fusion-Digital-Power-Designer-xxx.exe*. The xxx in the file name refers to the GUI release version.

Double click the executable installer file and follow the instructions to complete installation. In general, accept all the installation defaults. In order to have all of the GUI functions available, check all the boxes under *Select Additional Tasks* as shown in Figure 42.

🕞 Setup - Texas Instruments Fusion Digital Power Designer	
Select Additional Tasks Which additional tasks should be performed?	
Select the additional tasks you would like Setup to perform while installing Texas Instruments Fusion Digital Power Designer, then click Next.	
Additional icons:	^
Create a desktop icon	
Create a Quick Launch icon	
Other desktop shortcuts	_
🗹 Fusion Design Offline	-
SMBus I2C SAA Debug Tool	
UCD3xxx UCD9xxx Device GUI	
Additional Tasks:	
Add application directory to your system PATH	~
< Back Next >	Cancel

Figure 42. GUI Installation

After the installation, a quick launch button appears next to the start menu in the taskbar section containing shortcuts to commonly-used applications. Figure 43 shows the TI FDPD icon after the installation. Other icons, such as UCD3K Device GUI, are displayed on the desktop. For more information on the GUI installation, see the UCD3138CC64EVM-030 user's guide (SLUU886).



Figure 43. GUI Shortcut Location

13.1.3 USB-to-GPIO Adaptor Connection

CAUTION

Turn off the DC power source before connecting the USB-to-GPIO adaptor to avoid electrical shock.

Connect one end of the ribbon cable to the module, and connect the other end to the USB-to-GPIO (HPA172) interface adapter. Connect the mini connector of the USB cable to the USB interface adapter. Then connect the other end to the USB port on the host computer, as shown in Figure 41.

13.1.4 Launch the Designer GUI

Click the quick-launch shortcut icon located in the taskbar next to the start menu. When launched, the GUI searches for a device attached to the PMBus. If the attached device is found and communication between the GUI and device is successful, a similar-looking screen as shown in Figure 44 is seen. The following sections describes how to evaluate the module using the GUI.



Figure 44. Designer GUI Overview



13.1.5 Designer GUI Overview

The Designer GUI has four tabs on the left side of the workspace, as shown in Figure 44: *Configure*, *Design*, *Monitor*, and *Status*. After launching the GUI, the default tab is the *Monitor* tab. To open one of the three tabs, simply click on the desired tab.

Each tab of the EVM GUI has a different role. *Configure* configures the EVM settings through PMBus command. *Design* creates tuning control-loop parameters. *Monitor* monitors the board operation. *Status* shows faults and warnings that may occur.

13.2 Operation Monitoring

When the designer GUI launches, the *Monitor* tab is presented by default as shown in Figure 44. This tab provides a quick overview of operation status with some changeable settings. This tab also provides an oscilloscope-type plot view in real-time operation. The number of scope windows is adjusted by checking or un-checking the square boxes in the upper-left of the *Monitor* tab. Click on a box to show or hide the selected scope-plot windows.

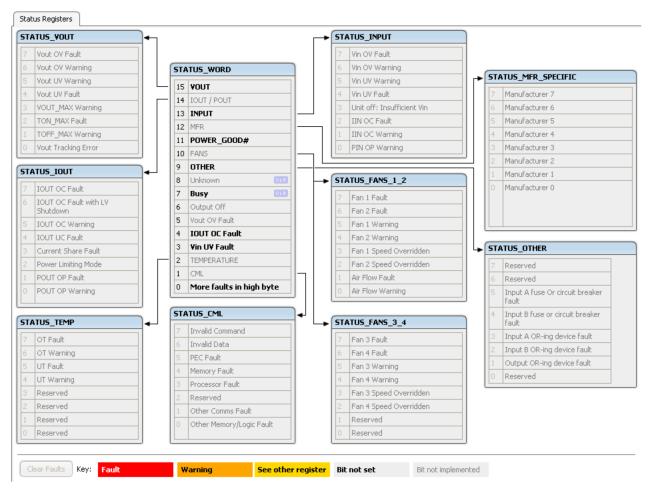


Figure 45. Designer GUI Status

13.3 Operation Status

Click the *Status* tab below the *Monitor* tab (see Figure 44) to view the EVM operation status shown as in Figure 45. All grayed entries are candidates that can be implemented. Those candidates in black represent current-operation status which indicate potential operation issues with either warning or fault indications. If a fault occurred, the corresponding entry is highlighted in red. Warnings, although not considered faults, remind the user that those entries could require attention.



13.4 Configuring EVM

The *Configure* tab allows the user to conveniently adjust the EVM feature setup without directly accessing the firmware. This tab also navigates the user through the various features of the converter within the GUI.

Command	Code	¥alue/Edit	Hex/Edit
▼ Configuration			
CPCC [MFR 36]	0xF4	Click 🗸	0×01 🗸
FREQUENCY_SWITCH	0x33	140.0 🚔 kHz	0×008C
YOUT_COMMAND	0x21	11.875 💭 V	0×17C0
VOUT_MODE	0x20	EXP -9	0x17
▼ Limits			
IIN_OC_FAULT_LIMIT	0×58	9.00 💭 A	0×0009
IOUT_OC_FAULT_LIMIT	0×46	41.00 🚔 A	0×0029
OT_FAULT_LIMIT	0×4F	70 🜩 ℃	0x0046
VOUT_OV_FAULT_LIMIT	0×40	14.000 📩 V	0×1C00
▼ Manufacturer Info			
CMD5_DCDC_NONPAGED [MFR 21]	0×E5	Click 🗸	0×10 🗸
CMD5_DCDC_PAGED [MFR 20]	0xE4	Click 🗸	0×00 🗸
DEVICE_ID [MFR 45]	0×FD	UCD3100ISO1	0×55 🗸
IC_DEVICE_ID	0×AD	UCD3138RGC	0x55 🗸
MFR_DATE	0×9D	111020	0x31 🗸
MFR_ID	0×99	TI	0x54 🗸
MFR_LOCATION	0x9C	Dallas, TX	0x44 🗸
MFR_MODEL	0×9A	UCD3138P5	0x55 🗸
MFR_REVISION	0×9B	E1	0x45 🗸
MFR_SERIAL	0×9E	XXXXX	0x58 🗸
PMBUS_REVISION	0×98	1.2,1.2 - Part	0x42
SETUP_ID [MFR 23]	0×E7	VERSIO 🗸	0x56 🗸
STATUS_BIT_MASK [MFR 34]	0xF2	0x22334 🗸	0x22 🗸

Command	Code	Value/Edit	Hex/Edit
▼ Status			
READ_DEBUG_BUFFER1 [MFR 32]	0×F0	Click 🗸	0×01 🗸
READ_FREQUENCY	0×95	140.0 kHz	0×008C
READ_IOUT	0x8C	6.00 A	0×0006
READ_TEMP_INTERNAL	0x8D	-31 °C	0×07E1
READ_YOUT	0×8B	2.682 V	0×055D
STATUS_BYTE	0×78	00000000 🗸	0×00
STATUS_WORD	0x79	Click 🗸	0×0000

Figure 46. GUI Supported PMBus Commands

13.4.1 GUI Supported PMBus Commands

Figure 47 shows the various GUI-based PMBus commands supported by the current version of the firmware. Use the built-in *Isolated Bit mask* generator to easily add additional standard commands. This tool generates a coded index that the GUI reads from the device to determine which PMBus commands are supported. To add a standard command, modify the bit mask and the GUI automatically displays the new command. For additional details on using this tool, please contact TI.



In the *Configure* tab, changing the configuration is simple. For example, to configure CPCC, access the CPCC control by clicking the drop-down arrow next to the Value/Edit box on the CPCC[MFR 36] line as shown in Figure 47. As previously mentioned, the maximum current is 35 A and the maximum power is 360 W. Please contact TI if any uncertainty exists that must be resolved. The CPCC feature is disabled by default.

Command	Code V	alue/Edit	Hex/Edit		
▼ Configuration					
CPCC [MFR 36]	0×F4	Click 🔽	0x01 🗸		_
FREQUENCY_SWITCH	0x33	140.0 🌻	PMAX:	360.0 🌩 W	
VOUT_COMMAND	0x21	11.875 🜲			
VOUT_MODE	0x20 E	XP -9	IMAX:	33.0 🕀 A	
▼ Limits			TON:	100.0 ਦ msec	
IIN_OC_FAULT_LIMIT	0x5B	9.00 🌲	Enable:	OFF 🔽	
IOUT_OC_FAULT_LIMIT	0x46	41.00 🚔	Timer:	OFF 🔽	
OT_FAULT_LIMIT	0×4F	70 🜩			
VOUT_OV_FAULT_LIMIT	0x40	14.000 🜩			:

Figure 47. Configure CPCC

13.5 Tuning the Control Loop Using GUI Design

The GUI is equipped with 3 different ways to program the UCD3138 digital control-loop compensator. Table 10 lists the three options, (a) complex zeros using K_0 , f_z , Q_z , and f_p ; (b) real zeros using K_0 , f_{z1} , f_{z2} , and f_p ; (c) device PID using K_p , K_i , K_d , and α .

In option (c), the compensator is described by device PID. In this context, K_p , K_i , K_d and α are the raw register values used to configure the positions of the poles and zeros of the compensator. SC is a gain scaling term. Although SC is normally set to zero, it provides additional gain for situations where the power-stage gain is low. PRD is used to configure the minimum operating period, and KCOMP is used to configure the maximum operating period. In the context of the compensator they are gain terms modifing the overall transfer function by a fixed value. Knowing the proper way to configure PRD and KCOMP varies based on the control topology implemented is important.

System Name	Transfer Functions
Complex zeros (K_0, f_z, Q_z, f_p)	$\frac{\frac{s^2}{(2 \times \pi \times f_z)^2} + \frac{s}{2 \times \pi \times f_z \times Q_z} + 1}{s}$
	$\frac{\frac{s}{2 \times \pi \times K_0} \times \left(\frac{s}{2 \times \pi \times f_p} + 1\right)}{\left(\frac{s}{2 \times \pi \times f_{z1}} + 1\right) \times \left(\frac{s}{2 \times \pi \times f_{z2}} + 1\right)}$
Real zeros $(K_0, f_{z1}, f_{z2}, f_p)$	$\frac{(2 \times \pi \times f_{z1}) (2 \times \pi \times f_{z2})}{\frac{s}{2 \times \pi \times K_0} \times \left(\frac{s}{2 \times \pi \times f_p} + 1\right)}$
Device PID (K _p , K _i , Kd, α)	$1000 \times \left(K_{p} + K_{i} \times \frac{1 + z^{-1}}{1 - z^{-1}} + K_{d} \times \frac{1 - z^{-1}}{1 - \alpha \times 2^{-8} \times z^{-1}}\right) \times 2^{-sc} \times KCOMP \times 2^{-19} \times \frac{1}{2^{4} \times (PRD + 1)}$

Table 10. Programming Digital Control Loop

14 Firmware Development for Phase-Shifted Full-Bridge Power Converter

Please contact TI for additional information regarding the UCD3138 firmware development for a digital phase-shifted full-bridge converter control.

15 References

- 1. UCD3138 Datamanual, Highly Integrated Digital Controller for Isolated Power (SLUSAP2)
- 2. UCD3138CC64EVM-030 Evaluation Module and User's Guide, *Programmable Digital Power Controller Control Card Evaluation Module* (<u>SLUU886</u>)
- 3. Reference Guide, UCD3138 Digital Power Peripherals Programmer's Manual (SLUU995)
- 4. Reference Guide, UCD3138 Monitoring and Communications Programmer's Manual (SLUU996)
- 5. Reference Guide, UCD3138 ARM and Digital System Programmer's Manual (SLUU994)
- 6. User's Guide, UCD3138 Isolated Power Fusion GUI, (please contact TI)

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As noted in the EVM User's Guide and/or EVM itself, this EVM and/or accompanying hardware may or may not be subject to the Federal Communications Commission (FCC) and Industry Canada (IC) rules.

For EVMs **not** subject to the above rules, this evaluation board/kit/module is intended for use for ENGINEERING DEVELOPMENT, DEMONSTRATION OR EVALUATION PURPOSES ONLY and is not considered by TI to be a finished end product fit for general consumer use. It generates, uses, and can radiate radio frequency energy and has not been tested for compliance with the limits of computing devices pursuant to part 15 of FCC or ICES-003 rules, which are designed to provide reasonable protection against radio frequency interference. Operation of the equipment may cause interference with radio communications, in which case the user at his own expense will be required to take whatever measures may be required to correct this interference.

General Statement for EVMs including a radio

User Power/Frequency Use Obligations: This radio is intended for development/professional use only in legally allocated frequency and power limits. Any use of radio frequencies and/or power availability of this EVM and its development application(s) must comply with local laws governing radio spectrum allocation and power limits for this evaluation module. It is the user's sole responsibility to only operate this radio in legally acceptable frequency space and within legally mandated power limitations. Any exceptions to this are strictly prohibited and unauthorized by Texas Instruments unless user has obtained appropriate experimental/development licenses from local regulatory authorities, which is responsibility of user including its acceptable authorization.

For EVMs annotated as FCC – FEDERAL COMMUNICATIONS COMMISSION Part 15 Compliant

Caution

This device complies with part 15 of the FCC Rules. Operation is subject to the following two conditions: (1) This device may not cause harmful interference, and (2) this device must accept any interference received, including interference that may cause undesired operation.

Changes or modifications not expressly approved by the party responsible for compliance could void the user's authority to operate the equipment.

FCC Interference Statement for Class A EVM devices

This equipment has been tested and found to comply with the limits for a Class A digital device, pursuant to part 15 of the FCC Rules. These limits are designed to provide reasonable protection against harmful interference when the equipment is operated in a commercial environment. This equipment generates, uses, and can radiate radio frequency energy and, if not installed and used in accordance with the instruction manual, may cause harmful interference to radio communications. Operation of this equipment in a residential area is likely to cause harmful interference in which case the user will be required to correct the interference at his own expense.

FCC Interference Statement for Class B EVM devices

This equipment has been tested and found to comply with the limits for a Class B digital device, pursuant to part 15 of the FCC Rules. These limits are designed to provide reasonable protection against harmful interference in a residential installation. This equipment generates, uses and can radiate radio frequency energy and, if not installed and used in accordance with the instructions, may cause harmful interference to radio communications. However, there is no guarantee that interference will not occur in a particular installation. If this equipment does cause harmful interference to radio or television reception, which can be determined by turning the equipment off and on, the user is encouraged to try to correct the interference by one or more of the following measures:

- Reorient or relocate the receiving antenna.
- Increase the separation between the equipment and receiver.
- · Connect the equipment into an outlet on a circuit different from that to which the receiver is connected.
- Consult the dealer or an experienced radio/TV technician for help.

For EVMs annotated as IC – INDUSTRY CANADA Compliant

This Class A or B digital apparatus complies with Canadian ICES-003.

Changes or modifications not expressly approved by the party responsible for compliance could void the user's authority to operate the equipment.

Concerning EVMs including radio transmitters

This device complies with Industry Canada licence-exempt RSS standard(s). Operation is subject to the following two conditions: (1) this device may not cause interference, and (2) this device must accept any interference, including interference that may cause undesired operation of the device.

Concerning EVMs including detachable antennas

Under Industry Canada regulations, this radio transmitter may only operate using an antenna of a type and maximum (or lesser) gain approved for the transmitter by Industry Canada. To reduce potential radio interference to other users, the antenna type and its gain should be so chosen that the equivalent isotropically radiated power (e.i.r.p.) is not more than that necessary for successful communication.

This radio transmitter has been approved by Industry Canada to operate with the antenna types listed in the user guide with the maximum permissible gain and required antenna impedance for each antenna type indicated. Antenna types not included in this list, having a gain greater than the maximum gain indicated for that type, are strictly prohibited for use with this device.

Cet appareil numérique de la classe A ou B est conforme à la norme NMB-003 du Canada.

Les changements ou les modifications pas expressément approuvés par la partie responsable de la conformité ont pu vider l'autorité de l'utilisateur pour actionner l'équipement.

Concernant les EVMs avec appareils radio

Le présent appareil est conforme aux CNR d'Industrie Canada applicables aux appareils radio exempts de licence. L'exploitation est autorisée aux deux conditions suivantes : (1) l'appareil ne doit pas produire de brouillage, et (2) l'utilisateur de l'appareil doit accepter tout brouillage radioélectrique subi, même si le brouillage est susceptible d'en compromettre le fonctionnement.

Concernant les EVMs avec antennes détachables

Conformément à la réglementation d'Industrie Canada, le présent émetteur radio peut fonctionner avec une antenne d'un type et d'un gain maximal (ou inférieur) approuvé pour l'émetteur par Industrie Canada. Dans le but de réduire les risques de brouillage radioélectrique à l'intention des autres utilisateurs, il faut choisir le type d'antenne et son gain de sorte que la puissance isotrope rayonnée équivalente (p.i.r.e.) ne dépasse pas l'intensité nécessaire à l'établissement d'une communication satisfaisante.

Le présent émetteur radio a été approuvé par Industrie Canada pour fonctionner avec les types d'antenne énumérés dans le manuel d'usage et ayant un gain admissible maximal et l'impédance requise pour chaque type d'antenne. Les types d'antenne non inclus dans cette liste, ou dont le gain est supérieur au gain maximal indiqué, sont strictement interdits pour l'exploitation de l'émetteur.

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This development kit is NOT certified as Confirming to Technical Regulations of Radio Law of Japan

If you use this product in Japan, you are required by Radio Law of Japan to follow the instructions below with respect to this product:

- Use this product in a shielded room or any other test facility as defined in the notification #173 issued by Ministry of Internal Affairs and Communications on March 28, 2006, based on Sub-section 1.1 of Article 6 of the Ministry's Rule for Enforcement of Radio Law of Japan,
- 2. Use this product only after you obtained the license of Test Radio Station as provided in Radio Law of Japan with respect to this product, or
- 3. Use of this product only after you obtained the Technical Regulations Conformity Certification as provided in Radio Law of Japan with respect to this product. Also, please do not transfer this product, unless you give the same notice above to the transferee. Please note that if you could not follow the instructions above, you will be subject to penalties of Radio Law of Japan.

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EVALUATION BOARD/KIT/MODULE (EVM) WARNINGS, RESTRICTIONS AND DISCLAIMERS

For Feasibility Evaluation Only, in Laboratory/Development Environments. Unless otherwise indicated, this EVM is not a finished electrical equipment and not intended for consumer use. It is intended solely for use for preliminary feasibility evaluation in laboratory/development environments by technically qualified electronics experts who are familiar with the dangers and application risks associated with handling electrical mechanical components, systems and subsystems. It should not be used as all or part of a finished end product.

Your Sole Responsibility and Risk. You acknowledge, represent and agree that:

- 1. You have unique knowledge concerning Federal, State and local regulatory requirements (including but not limited to Food and Drug Administration regulations, if applicable) which relate to your products and which relate to your use (and/or that of your employees, affiliates, contractors or designees) of the EVM for evaluation, testing and other purposes.
- 2. You have full and exclusive responsibility to assure the safety and compliance of your products with all such laws and other applicable regulatory requirements, and also to assure the safety of any activities to be conducted by you and/or your employees, affiliates, contractors or designees, using the EVM. Further, you are responsible to assure that any interfaces (electronic and/or mechanical) between the EVM and any human body are designed with suitable isolation and means to safely limit accessible leakage currents to minimize the risk of electrical shock hazard.
- 3. Since the EVM is not a completed product, it may not meet all applicable regulatory and safety compliance standards (such as UL, CSA, VDE, CE, RoHS and WEEE) which may normally be associated with similar items. You assume full responsibility to determine and/or assure compliance with any such standards and related certifications as may be applicable. You will employ reasonable safeguards to ensure that your use of the EVM will not result in any property damage, injury or death, even if the EVM should fail to perform as described or expected.
- 4. You will take care of proper disposal and recycling of the EVM's electronic components and packing materials.

Certain Instructions. It is important to operate this EVM within TI's recommended specifications and environmental considerations per the user guidelines. Exceeding the specified EVM ratings (including but not limited to input and output voltage, current, power, and environmental ranges) may cause property damage, personal injury or death. If there are questions concerning these ratings please contact a TI field representative prior to connecting interface electronics including input power and intended loads. Any loads applied outside of the specified output range may result in unintended and/or inaccurate operation and/or possible permanent damage to the EVM and/or interface electronics. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative. During normal operation, some circuit components may have case temperatures greater than 60°C as long as the input and output are maintained at a normal ambient operating temperature. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors which can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during normal operation, please be aware that these devices may be very warm to the touch. As with all electronic evaluation tools, only qualified personnel knowledgeable in electronic measurement and diagnostics normally found in development environments should use these EVMs.

Agreement to Defend, Indemnify and Hold Harmless. You agree to defend, indemnify and hold TI, its licensors and their representatives harmless from and against any and all claims, damages, losses, expenses, costs and liabilities (collectively, "Claims") arising out of or in connection with any use of the EVM that is not in accordance with the terms of the agreement. This obligation shall apply whether Claims arise under law of tort or contract or any other legal theory, and even if the EVM fails to perform as described or expected.

Safety-Critical or Life-Critical Applications. If you intend to evaluate the components for possible use in safety critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, such as devices which are classified as FDA Class III or similar classification, then you must specifically notify TI of such intent and enter into a separate Assurance and Indemnity Agreement.

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